



**SOPHION**

**SG2002**

## **Preliminary Datasheet**

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Releasedate: 2023-12-15



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## Revision history

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Revision	Date	Description
1.0	2023/12/15	Preliminary release 1.0-alpha



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# 1 product description

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## 1.1 Overview

SG2002 is a high-performance, low-power chip launched for edge intelligent surveillance IP cameras, smart cat-eye door locks, video doorbells, home intelligence and other product fields. It integrates H.264 video compression codec, H.265 Video compression encoder and ISP; supports HDR wide dynamic range, 3D noise reduction, defogging, lens distortion correction and other image enhancement and correction algorithms to provide customers with professional-level video image quality.

The chip also integrates a self-developed TPU, which can provide 1.0TOPS of computing power under 8-bit integer operations. The specially designed TPU scheduling engine can efficiently provide extremely high bandwidth data flow to all tensor processor cores. In addition, it also provides users with a powerful deep learning model compiler and software SDK development package. Mainstream deep learning frameworks, such as Caffe and Tensorflow, can be easily ported to its platform.

In addition, it also provides secure startup, secure updates, secure encryption, etc., to help users from development, mass production, Product applications, providing a range of security solutions.

An 8-bit MCU subsystem is integrated into the chip, which can replace the general external MCU to save BOM cost and power consumption.





## 1.2 Architecture

### 1.2.1 Overview

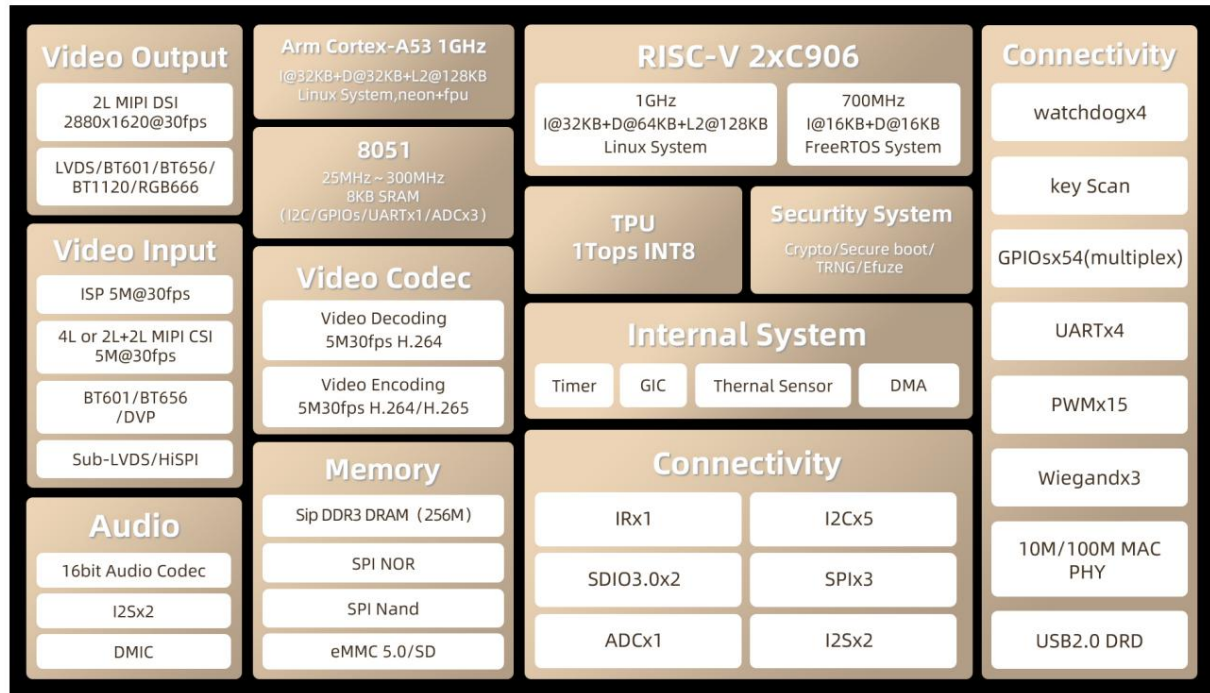


chart 1-1 SG2002 block diagram

### 1.2.2 Processor core

I Main processor RISCVC906@1.0Ghz.

- o 32KBI-cache, 64KBD-Cache o Integrated

- vector (Vector) and floating point operation unit (FPU). I Main

processor ARM Cortex-A53@1.0GHz

- o 32KBI-cache,32KBD-cache

- o 128KBL2 cache

- o Support Neon and floating point operation FPU

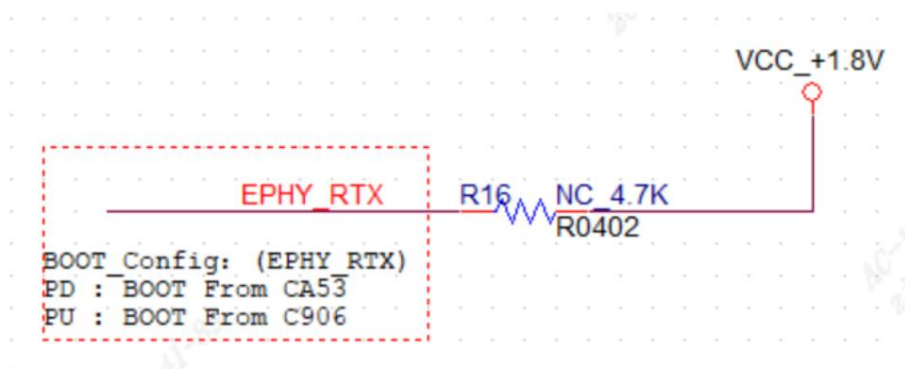
I Co-processor RISCVC906@ 700Mhz o Integrated

- floating point unit (FPU).

The main processor RISCVC906@1.0Ghz and the main processor ARM Cortex-A53@1.0GHz can be switched through the pin GPIO\_RTX\_\_EPHY\_RTX. The switching logic is:

Low-----ARM Cortex-A53@1.0GHz High-----

RISCVC906 @1.0Ghz



### 1.2.3 TPU

I Built-in TPU , The computing power reaches ~1.0TOPS INT8

supports mainstream neural network architectures: Caffe, Pytorch, TensorFlow (Lite), ONNX and MXNet I Can realize pedestrian detection (PedestrianDetection), face detection (FaceDetection), face recognition and living (Facerecognition), body detection (Faceanti - spoofing) and other video structuring applications.

### 1.2.4 Video codec

I H.264Baseline/Main/Highprofile I H.265Mainprofile

I H.264/H.265 supports both I

frame and P frame I MJPEG/JPEGbaseline I

H.264 codec maximum resolution:

2880x1620 (5M) I H.265 encoding Maximum resolution:

2880x1620 (5M) I H.264 encoding and decoding performance

n

2880x1620@30fps+720x576@30fps n 1920x1080@30fps

encoding + 1920x1080@30fps decoding I H.265 encoding performance n

2880x1620@30fps+720x576@30fps I JPEG Max Codec

performance n 2880x1620@30fps

I Supports multiple rate control modes such as CBR/VBR/FIXQP.

I Supports Region of Interest (ROI) coding

### 1.2.5 Video interface (SG2002)

I Input n

supports two video inputs at the same time (mipi2L+1L)



n Support MIPI, Sub-LVDS, HiSPI and other serial interfaces.  
 n Support 8/10/12bit RGB Bayer video input. n Support  
 BT.656 n Support AHD  
 multi-channel mixed BT format. n Support  
 SONY, OnSemi, OmniVision and other high-definition CMOS sensors n Supply  
 The programmable frequency output is used by the sensor as a  
 reference clock. n supports a maximum width of 2880 and a maximum resolution of 5M (2688x1944, 2880x1620)

#### I Output

supports a variety of serial and parallel screen display  
 specifications. n Supports serial interfaces  
 such as MIPI. n Supports parallel interfaces such as BT656, BT601 (8bit), BT1120,  
 8080, etc. n Supports SPI output interface.

### 1.2.6 ISP and image processing

I Image and video 90 degree, 180 degree, 270 degree  
 rotation I Image and video Mirror, Flip function  
 I Video 2-layer OSD overlay I  
 Video 1/32~32x zoom function I 3A (AE/  
 AWB/AF) algorithm I Fixed pattern  
 noise elimination, Dead pixel correction I Lens  
 shadow correction, lens distortion correction, purple fringe  
 correction I Direction adaptive  
 demosaic I Gamma correction, (regional/global) dynamic contrast enhancement, color  
 management and enhancement  
 I Area adaptive defogging I Bayer noise reduction, 3D reduction Noise,  
 detail enhancement and  
 sharpening enhancement I Local Tonemapping I  
 Sensor self-bandwidth dynamic  
 and 2 frame width dynamic  
 I Two-axis digital image anti-shake I Lens distortion correction I ISP tuning tools for PC

### 1.2.7 CV hardware acceleration engine

I The mixed mode of software and hardware supports some OpenCV libraries. I  
 The mixed mode of software and hardware supports some IVE libraries.



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### 1.2.8 Audio codec (SG2002)

| Integrated AudioCODEC, supports 16bit audio source/voice input and output. | Integrated mono microphone input. | Integrated mono output. (An external power amplifier is required to drive the speaker) | Internally integrated another microphone is directly connected to the output channel, which is convenient Implement AEC. | Software audio codec protocol (G.711, G.726, ADPCM) | Software supports audio 3A (AEC, ANR, AGC) functions.

### 1.2.9 Network interface

| The Ethernet module provides 1 EthernetMAC. EthernetMAC , Realize the reception and sending of network data. with built-in 10/100Mbps FastEthernetTransceiver can work in 10/100Mbps full-duplex or half-duplex mode.

### 1.2.10 Security system module

| Hardware implements AES/DES/SM4 multiple encryption and decryption algorithms | Hardware implements HASH (SHA1/SHA256) hash algorithm | Hardware implements random number generator | Internally integrated 2KbiteFuse logical space

### 1.2.11 Intelligent and safe operating environment

| Support the establishment of trust chain: provide the basis for a secure environment and the basis for a trusted environment, such as hardware security equipment Configuration and root of trust | Support secure boot for secure hardware and software protection functions | Support data encryption security: data encryption program, computing core encryption | Support software and firmware verification process: confirm software credibility and integrity, including booting and Load the signature verification program | Support secure storage and transmission: protect external data storage and exchange | Support secure updates



### 1.2.12 Peripheral interface (SG2002)

- | Integrated POR, Power sequence | 4 single-ended ADC (3 nodiedomain) | 6 I2C (1 nodiedomain)
- | 3 SPI | 5 sets of UART (1 nodiedomain) | 4 sets (15 channels)
- | PWM | 2 SDIO interfaces. One supports 3V Connect to SD3.0 Card (support maximum capacity SDXC2TB, support speed is UHS-I) One supports 1.8V/3.0V to connect to other SDIO3.0 devices. (Support speed is UHS-I)
- | 66 GPIO interface (14 nodiedomain) | Integrated keyscan and Wiegand | Integrated MACPHY supports 10/100Mbps full-duplex or half-duplex mode.
- | One USB Host/device interface

### 1.2.13 External memory interface

- | Built-in DRAM n SG2002 DDR3 16bit x1, maximum speed up to 1866Mbps, capacity 2Gbit (256MB)
- | SPINOR flash interface (1.8V/3.0V) n Supports 1, 2, 4-wire mode. n Supports a maximum of 256MByte. | SPINandflash interface (1.8V/3.0V) n Supports 1KB/2KB/4KB page (corresponding maximum capacity 16GB/32GB /64GB) n Use the ECC module built into the device itself. | eMMC4.5 interface (1.8V/3.0V)
- SD0EMMC shares a common power supply. Because the SD card defaults to 3V, there is SD card, it is not suitable for connecting to 1.8VeMMC. n 4bit interface. n Supports HS200 n Maximum supported capacity 2TB

### 1.2.14 SDK

- | Linux-5.10-based SDK



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### 1.2.15 Chip physical specifications

#### I Power

consumption n 1080P+Videoencode+AI: ~500mW n Other

scenarios: TBD | Operating

voltage n Core voltage

is 0.9V n IO voltage is 1.8V and

3.0V n DDR voltage is as shown in the

table below. u SG2002 =1.35V |

Package n Use QFN package,

the package

size is 9mmx9mmx0.9mm. The pin pitch is 0.35mm. The total number of pins is 88

## 1.3 Startup and upgrade mode

### 1.3.1 Overview

The chip is started by the built-in ROM (BOOTROM). When the chip is reset, it will detect whether there is a weak pull-up or weak pull-down on the two pins (EMMC\_DAT3, EMMC\_DAT0) to confirm the type of memory device currently selected. Secure boot

chips will be verified during boot and chip upgrade to ensure that the software being executed or upgraded is safe.

### 1.3.2 Correspondence between startup mode and corresponding signal latch value

| Support startup by SPINorFlash (EMMC\_DAT3pulldown, EMMC\_DAT0pullup) | Support startup by SPINandFlash (EMMC\_DAT3pulldown, EMMC\_DAT0pulldown) | Support startup by eMMC (EMMC\_DAT3pullup, EMMC\_DAT0pullup)

Note.SG2002 Because SD0 and eMMCdomain share IOpower. Because the SD card defaults to 3.0V, and Most eMMC is 1.8V, so it basically does not support eMMC unless SD0 does not connect to the SD card.

### 1.3.3 Image burning mode.

| Supports image burning through SD card. |

Supports image burning through USBdevicemode. | If there is an

image in flash, the software supports software upgrade through the network



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### 1.3.4 Secure boot

| Support secure boot and upgrade

| AES/DES/SM4 hardware encryption and

decryption. | SHA/TRNG/SecureEfuse security hardware.

## 1.4 Address space mapping

Start address [31:0]	End address [31:0]	Space function	Space size (Byte)
0x01000000	0x017FFFFFFF	reserved	8M
0x01800000	0x018FFFFFFF	reserved	
0x01900000	0x01900FFF	ap_mailbox	4K
0x01901000	0x01901FFF	ap_system_ctrl	4K
0x01902000	0x019EFFFF	reserved	
0x01F00000	0x01F0FFFF	reserved	64K
0x01F10000	0x01FFFFFF	reserved	
0x02000000	0x02FFFFFF	reserved	64K
0x03000000	0x03000FFF	TOP_MISC control register	4K
0x03001000	0x03001FFF	PINMUX control register	4K
0x03002000	0x03002FFF	CLKGEN/PLL control register	4K
0x03003000	0x03003FFF	RSTGEN control register	4K
0x03004000	0x03005FFF	reserved	
0x03006000	0x03006FFF	reserved	4K
0x03007000	0x03008FFF	reserved	
0x03009000	0x03009FFF	reserved	4K
0x0300A000	0x0300AFFF	reserved	4K
0x0300B000	0x0300BFFF	reserved	
0x03010000	0x03010FFF	WATCHDOG0 control register	4K
0x03011000	0x03011FFF	WATCHDOG1 control register	4K
0x03012000	0x03012FFF	WATCHDOG2 control register	4K
0x03020000	0x03020FFF	GPIO0 control register	4K
0x03021000	0x03021FFF	GPIO1 control register	4K
0x03022000	0x03022FFF	GPIO2 control register	4K
0x03023000	0x03023FFF	GPIO3 control register	4K
0x03024000	0x0302FFFF	reserved	
0x03030000	0x03030FFF	WGN0 control register	4K
0x03031000	0x03031FFF	WGN1 control register	4K
0x03032000	0x03032FFF	WGN2 control register	4K
0x03033000	0x0303FFFF	reserved	
0x03040000	0x0304FFFF	KEYSCAN control register	64K
0x03050000	0x0305FFFF	EFUSE control register	64K
0x03060000	0x03060FFF	PWM0 control register	4K
0x03061000	0x03061FFF	PWM1 control register	4K
0x03062000	0x03062FFF	PWM2 control register	4K
0x03063000	0x03063FFF	PWM3 control register	4K
0x03064000	0x0309FFFF	reserved	





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0x030A0000	0x030AFFFF	TIMER control register	64K
0x030C0000	0x030CFFFF reserved		
0x030D0000	0x030D0FFF reserved		4K
0x030D1000	0x030D1FFF reserved		4K
0x030D2000	0x030D2FFF reserved		4K
0x030D3000	0x030DFFFF reserved		
0x030E0000	0x030EFFFF	TEMPSEN control register	64K
0x030F0000	0x030FFFFF	SARADC control register	64K
0x04000000	0x0400FFFF	I2C0 control register	64K
0x04010000	0x0401FFFF	I2C1 control register	64K
0x04020000	0x0402FFFF	I2C2 control register	64K
0x04030000	0x0403FFFF	I2C3 control register	64K
0x04040000	0x0404FFFF	I2C4 control register	64K
0x04050000	0x0405FFFF reserved		
0x04060000	0x0406FFFF	SPI_NAND control register	64K
0x04070000	0x0407FFFF	ETH0 control register	
0x04080000	0x0408FFFF reserved		
0x04100000	0x04107FFF	I2S0 control register	64K
0x04108000	0x0410FFFF	I2SGlobal control register	64K
0x04110000	0x0411FFFF	I2S1 control register	64K
0x04120000	0x0412FFFF	I2S2 control register	64K
0x04130000	0x0413FFFF	I2S3 control register	64K
0x04140000	0x0414FFFF	UART0 control register	64K
0x04150000	0x0415FFFF	UART1 control register	64K
0x04160000	0x0416FFFF	UART2 control register	64K
0x04170000	0x0417FFFF	UART3 control register	64K
0x04180000	0x0418FFFF	SPI0 control register	64K
0x04190000	0x0419FFFF	SPI1 control register	64K
0x041A0000	0x041AFFFF	SPI2 control register	64K
0x041B0000	0x041BFFFF	SPI3 control register	64K
0x041C0000	0x041CFFFF	UART4 control register	64K
0x041D0000	0x041DFFFF	AUDSRC control register	64K
0x041E0000	0x041EFFFF reserved		
0x04300000	0x0430FFFF	eMMC control register	64K
0x04310000	0x0431FFFF	SD0 control register	64K
0x04320000	0x0432FFFF	SD1 control register	
0x04330000	0x0433FFFF	DMA control register	64K
0x04340000	0x0434FFFF	USB control register	64K
0x04350000	0x0435FFFF reserved		
0x04400000	0x0441FFFF	ROM memory space	128K
0x04420000	0x0442FFFF reserved		



0x05000000	0x05000FFF reserved		4KB
0x05020000	0x05020FFF	RTCSYS_Timer control register	4KB
0x05021000	0x05021FFF	RTCSYS_GPIO control register	4KB
0x05022000	0x05022FFF	RTCSYS_UART control register	4KB
0x05023000	0x05023FFF	RTCSYS_INTR control register	4KB
0x05024000	0x05024FFF	RTCSYS_MBOX control register	4KB
0x05025000	0x05025FFF	RTCSYS_CTRL control register	4KB
0x05026000	0x05026FFF	RTCSYS_CORE	4KB
0x05027000	0x05027FFF	RTCSYS_IO control register	4KB
0x05028000	0x05028FFF	RTCSYS_OSC control register	4KB
0x05029000	0x05029FFF reserved		4KB
0x0502A000	0x0502AFFF	RTCSYS_32kless control register	4KB
0x0502B000	0x0502BFFF	RTCSYS_I2C control register	4KB
0x0502C000	0x0502CFFF	RTCSYS_SAR control register	4KB
0x0502D000	0x0502DFFF	RTCSYS_WDT control register	4KB
0x0502E000	0x0502EFFF	RTCSYS_IRRX control register	4KB
0x05200000	0x053FFFFF	RTCSYS_SRAM	8KB
0x05400000	0x057FFFFF	RTCSYS_SPINOR	4MB
0x08000000	0x08001FFF reserved		8K
0x08004000	0x08005FFF	DDRController control register	8K
0x08006000	0x08007FFF reserved		8K
0x08008000	0x08009FFF	DDRAXIMonitor control register	8K
0x0800A000	0x0800BFFF	DDRGlobal control register	8K
0x08010000	0x08011FFF reserved		8K
0x08012000	0x08013FFF reserved		8K
0x08014000	0x09FFFFFF reserved		
0x0A000000	0x0A07FFFF	ISP control register	512K
0x0A080000	0x0A0803FF	sc_top control register	1K
0x0A080400	0x0A080BFF reserved		2K
0x0A080C00	0x0A080CFF	osdenc control register	256B
0x0A080D00	0x0A080FFF	Reserved	768B
0x0A081000	0x0A081FFF reserved		4K
0x0A082000	0x0A082FFF	img_v control register	4K
0x0A083000	0x0A083FFF	img_d control register	4K
0x0A084000	0x0A084FFF	sc_d control register	4K
0x0A085000	0x0A085FFF	sc_v1 control register	4K
0x0A086000	0x0A086FFF	sc_v2 control register	4K
0x0A087000	0x0A087FFF	sc_v3 control register	4K
0x0A088000	0x0A088FFF	DISP control register	4K
0x0A089000	0x0A089FFF	Reserved	4K
0x0A08A000	0x0A08AFFF	dsi_mac control register	4K



0x0A08B000	0x0A08BFFF cmdq control register	4K
0x0A08C000	0x0A08CFFF reserved	4K
0x0A08D000	0x0A08DFFF reserved	4K
0x0A08E000	0x0A09FFF reserved	72K
0x0A0A0000	0x0A0AFFFF IVE control register	64K
0x0A0A0000	0x0A0BFFF reserved	64K
0x0A0C0000	0x0A0C1FFF ldc control register	8K
0x0A0C2000	0x0A0C3FFF VI0/MIPI_RX0 control register	8K
0x0A0C4000	0x0A0C5FFF VI1/MIPI_RX1 control register	8K
0x0A0C6000	0x0A0C7FFF VI2/MIPI_RX2 control register	8K
0x0A0C8000	0x0A0C9FFF VIPSYS control register	8K
0x0A0CA000	0x0A0CFFF reserved	24K
0x0A0D0000	0x0A0D0FFF CSI_PHY control register	4K
0x0A0D1000	0x0A0D1FFF DSI_PHY control register	4K
0x0A0D2000	0x0AFFF reserved	
0x0B000000	0x0B00FFFF JPEGcodec control register	64K
0x0B010000	0x0B01FFFF H.264codec control register	64K
0x0B020000	0x0B02FFFF H.265codec control register	64K
0x0B030000	0x0BFFFF reserved	
0x0C000000	0x0FFFFFF reserved	
0x10000000	0x1FFFFFF SPI_NOR memory space	256M
0x30000000	0x7FFFFFF reserved	
0x80000000	0xFFFFFFFF DDR memory space	2G

\*Reading and writing operations on the reserved address space may produce unpredictable results.



## 2 Hardware features

### 2.1 Package and pin distribution

#### 2.1.1 Package SG2002

SG2002 uses QFN package, the package size is 9mmx9mmx0.9mm. The pin pitch is 0.35mm.

The total number is 88. Please refer to the figure below for detailed package dimensions.

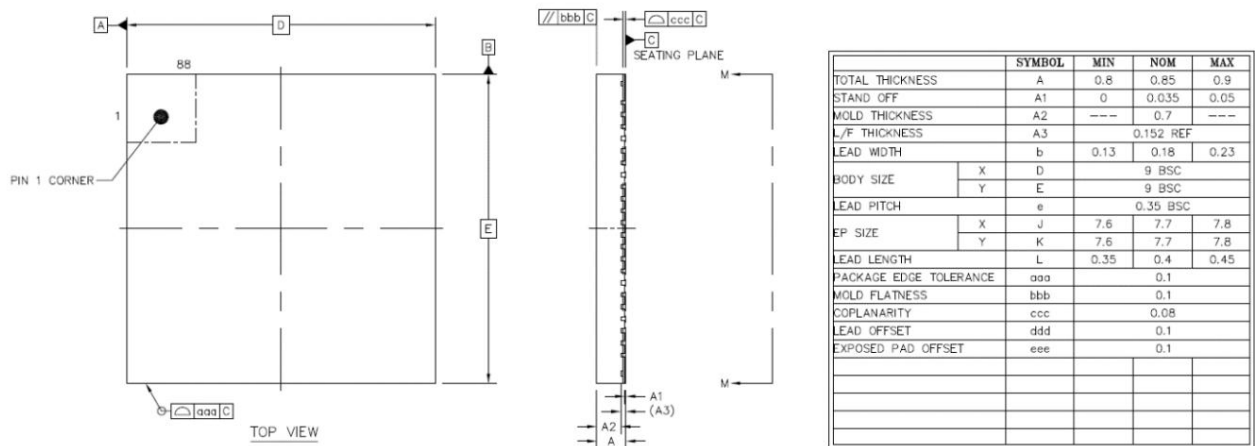


chart 2-1 SG2002 Package appearance dimegsions top view

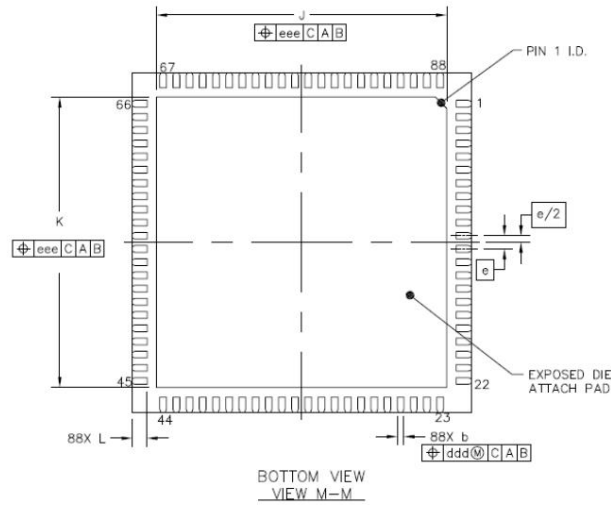


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	SYMBOL	MIN	NOM	MAX
TOTAL THICKNESS	A	0.8	0.85	0.9
STAND OFF	A1	0	0.035	0.05
MOLD THICKNESS	A2	---	0.7	---
L/F THICKNESS	A3		0.152 REF	
LEAD WIDTH	b	0.13	0.18	0.23
BODY SIZE	X	D	9 BSC	
	Y	E	9 BSC	
LEAD PITCH	e	0.35 BSC		
EP SIZE	X	J	7.6	7.7
	Y	K	7.6	7.7
LEAD LENGTH	L	0.35	0.4	0.45
PACKAGE EDGE TOLERANCE	aaa	0.1		
MOLD FLATNESS	bbb	0.1		
COPLANARITY	ccc	0.08		
LEAD OFFSET	ddd	0.1		
EXPOSED PAD OFFSET	eee	0.1		

chart 2-2.SG2002 Package appearance dimensions bottom view

### 2.1.2 Pin distribution SG2002

Pin No.	Pin Name	Pin No.	Pin Name
88	PAD_MIP1_TXP0	66	VDD33A_ETH_USB
87	PAD_MIP1_TXM0	65	PAD_ETH_RXM__EPHY_TXP
86	PAD_MIP1_TXP1	64	PAD_ETH_RXP__EPHY_TXN
85	PAD_MIP1_TXM1	63	PAD_ETH_TXM__EPHY_RXP
84	PAD_MIP1_TXP2	62	PAD_ETH_TXP__EPHY_RXN
83	PAD_MIP1_TXM2	61	VDDC
82	VDD18A_MIP1	60	USB_VBUS_DET
81	PAD_MIP1RX0P	59	ADC1
80	PAD_MIP1RX0N	58	PMW0_BUCK
79	PAD_MIP1RX1P	57	VDDIO_SD1
78	PAD_MIP1RX1N	56	SD1_CLK
77	PAD_MIP1RX2P	55	SD1_CMD
76	PAD_MIP1RX2N	54	SD1_D0
75	PAD_MIP1RX3P	53	SD1_D1
74	PAD_MIP1RX3N	52	SD1_D2
73	PAD_MIP1RX4P	51	SD1_D3
72	PAD_MIP1RX4N	50	VDDC
71	VDDC	49	PMW_GPIO2
70	USB_DM	48	PMW_GPIO1
69	USB_DP	47	PMW_GPIO0
68	VDD18A_USB_PLL_ETH	46	XTAL_XOUT
67	GPIO_RTX__EPHY_RTX	45	XTAL_XIN
1	VSS18A_AUD		
2	PAD_AUD_AINL_MIC		
3	PAD_AUD_AVREF		
4	PAD_AUD_AOUTR		
5	VDD18A_AUD		
6	SD0_CLK		
7	SD0_CMD		
8	SD0_D0		
9	VDDC		
10	SD0_D1		
11	SD0_D2		
12	SD0_D3		
13	VDDIO_SD0_EMMC		
14	SD0_CD		
15	SD0_PWR_EN		
16	VDDC		
17	SPK_EN		
18	UART0_TX		
19	UART0_RX		
20	EMMC_DAT2		
21	EMMC_CLK		
22	EMMC_DAT0		
23	EMMC_DAT3		
24	EMMC_CMD		
25	EMMC_DAT1		
26	JTAG_CPU_TMS		
27	JTAG_CPU_TCK		
28	IIC0_SCL		
29	IIC0_SDA		
30	AUX0		
31	VDDQ_DRAM		
32	VDDQ		
33	VDDQ		
34	VDDQ_DRAM		
35	GPIO_ZQ__PAD_ZQ		
36	VDDIO_RTC		
37	VDDC_RTC		
38	PMW_VBAT_DET		
39	PMW_RSTN		
40	PMW_SEQ1		
41	PMW_SEQ2		
42	PTTEST		
43	PMW_WAKEUP0		
44	PMW_BUTTON1		



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chart **2-3 SG2002** Pin layout diagram

## 2.2 Description of pin information

Please refer to SG2002\_PINOUT\_CN.xlsx



### 2.3 Welding process recommendations

Please refer to chart 2-4 for the lead-free reflow soldering process curve.

SG2002 Please refer to PureSn

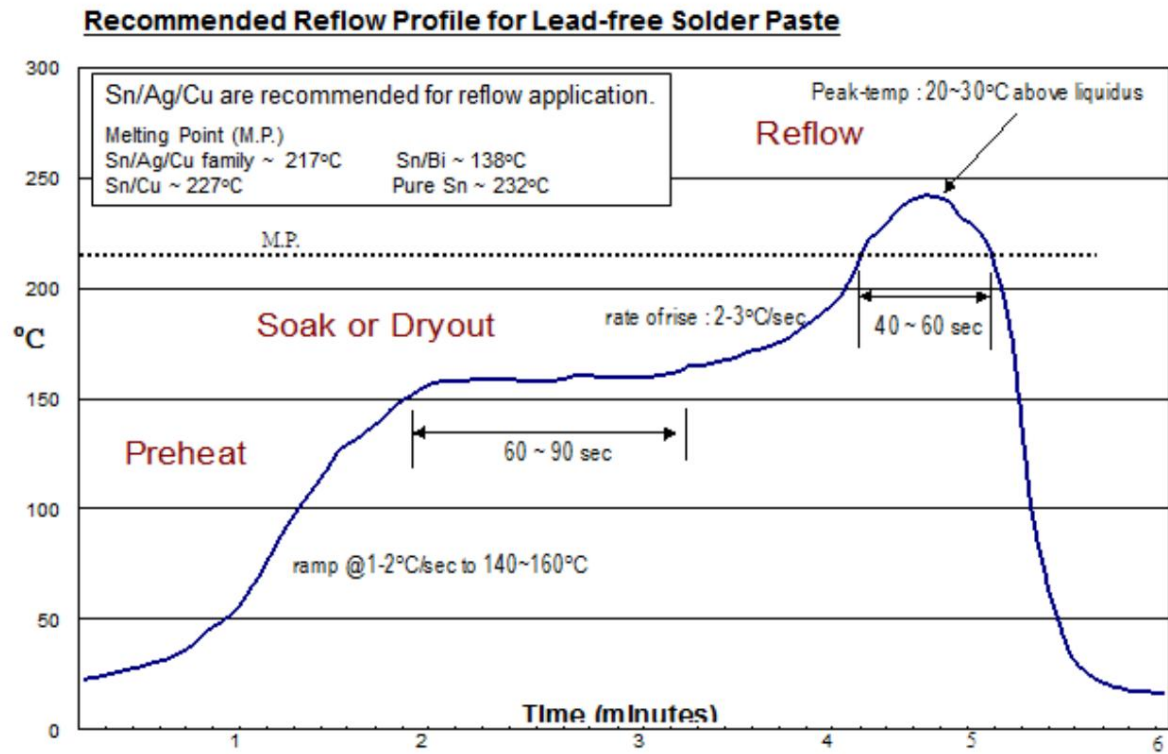


chart 24 Lead-free reflow soldering process curve

Please refer to Table 2y1 for lead-free reflow soldering process parameters.

The following parameters are only recommended values for reference, and the client needs to make corresponding adjustments based on actual production conditions.

sheet 2 1 Lead-free reflow soldering cap parameters

Regional time heating rate peak temperature preheating zone (40~150o C) 60~120sc	cooling rate
1~2o C/sec Average temperature zone (150~200o C) 60~90sec	
< 1o C/sec	
Reflow area (>melting point 20~30o C) 40~60sec 2~3o C/sec	Sn/Ag/Cu237~ 247oC Sn/Cu247~ 257oC PureSn252~262o C
cooling zone (Tmax~Also)	1~4o C/sec

Due to environmental protection reasons, parameters for lead-containing reflow soldering are currently not available.

## 2.4 Moisture sensitive parameters

### 2.4.1 Moisture-proof packaging of Shuuneng products

This chapter formulates the principles for the storage and soldering of chips (moisture-sensitive products).

Related terms | Floorlife (opening storage time): refers to the period between unpacking the moisture-proof packaging and reflowing in an environment <math><30^{\circ}\text{C}/60\% \text{RH}</math> Maximum length of stay allowed.

| Shelflife (sealed storage time): the normal storage time after the moisture-proof packaging is sealed.

#### 2.4.1.1 Packaging information

The moisture-proof vacuum bag contains (1) chip and tray. (2) drying bag (3) humidity card (HIC)



chart 2-5 Vacuum drying packaging information



TRAY 10 + 1 STACK 打帶方式:三短一長  
STRAP METHOD:3S1L



乾燥包  
DESICCANT

濕度卡  
HUMIDITY INDICATOR CARD

chart **2-6** Drying package humidity card chip and **tray** plate

#### 2.4.1.2 Incoming inspection of moisture-sensitive products

After opening the vacuum moisture-proof bag before SMT, check the humidity card. There are many different styles of humidity cards. But if it shows If it is exposed to moisture, it must be baked before SMT can be used. Please see Table 2-3 for the relevant baking time and temperature parameters.

If repackaged after opening and not exposed to an environment <30o C/60%RH for more than 2 hours, you can only replace it. After changing the drying bag, carry out vacuum drying and packaging. If it exceeds 2 hours, it is recommended to re-bake and replace the drying bag before resealing. Seal packaging.

#### 2.4.1.3 Storage and use. (Refer to JEDEC J-STD-033)

##### I Sealed storage time.(Shelflife)

Sealed vacuum moisture-proof bags, stored in an environment of 40o C/90%RH, can be stored for at least 12 months.

##### I Storage time after opening.(Floorlife)

Before SMT, the hygrometer shows that there are no damp components after opening. In an environment of 30o C/60%RH, drying is not required.

The time for direct use after baking is as shown in Table 2-2 Level 3 (the Floorlife rating of this chip is Level 3)

sheet **2-2** Humidity classification and storage time after opening (**floorlife**)

**Moisture classification level and floor life**

Level	Floor Life (out of bag) at factory ambient $\leq 30\text{ }^{\circ}\text{C}/60\%\text{ RH}$ or as stated
1	Unlimited at $\leq 30\text{ }^{\circ}\text{C}/85\%\text{RH}$
2	1 year
2a	4 weeks
3	168 hours
4	72 hours
5	48 hours
5a	24 hours
6	Mandatory bake before use. After bake, must be reflowed within the time limit specified on the label

**2.4.1.4 Rebaking**

If it is found that it has become damp after opening, it should be baked first before SMT, or if it is to be put back into the vacuum package. The baking temperature should be

For temperature and time, please refer to

Table 2-3. After baking and moisture-proof sealing, shelflife can be recalculated.

After baking, if it is not sealed against moisture, please refer to the storage time (floorlife)

sheet **2 · 3** Baking temperature and timetable

Package Thickness	Level	Bake @ $125\text{ }^{\circ}\text{C}$	Bake @ $40\text{ }^{\circ}\text{C} \leq 5\%\text{ RH}$
$\leq 1.4\text{ mm}$	2a	4 h.	5 days
	3	7 h.	11 days
	4	9 h.	13 days
	5	10 h.	14 days
	5a	14 h.	19 days
$\leq 2.0\text{ mm}$	2a	18 h.	21 days
	3	24 h.	33 days
	4	31 h.	43 days
	5	37 h.	52 days
	5a	48 h.	68 days
$\leq 4.0\text{ mm}$	2a	48 h.	67 days
	3	48 h.	67 days
	4	48 h.	68 days
	5	48 h.	68 days
	5a	48 h.	68 days



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## 2.5 Electrical performance parameters

### 2.5.1 Power consumption parameters

Typical scenario: 1080P+VideoEncode+AI~500mW

Other scenes: TBD

### 2.5.2 Temperature and thermal resistance parameters (SG2002)

The thermal resistance of the chip ThetaJA, JB, JC values. According to the results of JEDEC2s2pPCB, Table 2-4

sheet 2 4 SG2002 Thermal resistance parameters

PCB Condition	Package Size(mm)	ThetaJA(C/W)			PsiJt (C/W)	ThetaJC (C/W)	ThetaJB (C/W)
		0m/s	1m/s	2m/s			
JEDEC 2s2pPCB	9x9	20.3	15.9	14.8	0.17	6.9	5.32

The temperature-related parameters of the chip are shown in Table 2-5

sheet 2 5 Temperature related parameters

	Minimum	Maximum	Note
Working environment temperature $T_{amb}$ chip			1
junction temperature $T_{junc}$ recommended value	-30o C	70o C 85o C~105o	2
destructive junction temperature	-30o C -40o C	C +125o C	3,4

- The maximum working environment temperature, without violating the junction temperature, depends on the power consumption and heat dissipation conditions of the scenario.
- The recommended range of chip junction temperature mainly considers that when the temperature is too high, thermal may be caused due to poor heat dissipation conditions. run-away causes the temperature to be out of control and enter the destructive junction temperature range and damage the chip. In addition, working at high temperatures for a long time will also It will slightly accelerate chip aging and reduce the service life.
- The guaranteed junction temperature of the DRAM used is only -40o C~115o C. If it exceeds the range, the content in the DRAM cannot be guaranteed to be complete. sex.
- When the chip operates at a destructive junction temperature, it may cause irreversible physical damage to the chip.



### 2.5.3 Destructive voltage

The destructive voltage parameters are shown in Table 2-6. When working above the destructive voltage, irreversible physical damage may be caused.

sheet 2 6 Destructive voltage parameters (SG2002)

Parameter		Max	Unit
VDDC	Core power	1.05V	IN
VDDC_RTC	Core power for RTC domain (comes with LDO)		
VDD18A_AUD	Analog power for Audio ADC/DAC	1.98	IN
VDD18A_USB_PLL_ETH	Analog power for USB, PLL, ETH, efuse	1.98	IN
VDD18A_MIPI	Analog power for MIPI	1.98	IN
VDD33A_ETH_USB	Analog power for Ethernet PHY, USB PHY	3.465	IN
VDDIO_SD0_EMMC	IO power for EMMC & SD0 domain	3.465	IN
VDDIO_SD1	IO power for SD1 domain	3.465	IN
VDDIO_RTC	IO power for RTC domain (backup power)	1.98	IN
VDDQ	IO & DRAM Power for DDR2/DDR3L/DDR3	1.65	IN
VDDQ_DRAM			

### 2.5.4 Power on and off sequence (SG2002)

In principle, chips can be divided into the following groups. The power domain of the same group is powered on/off at the same time. Different groups, according to the following conditions:

Separate the power-on and power-off times.

#### I Always on domain

- n VDDIO\_RTC (1.8V)
- n VDDC\_RTC (0.9V) (built-in LDO)
- n VDDIO\_SD1

#### I Core power domain

- n VDDC

#### I 1.8V IO domain

- n VDD18A\_AUD (analog)
- n VDD18A\_USB\_PLL\_ETH (analog)
- n VDD18A\_MIPI (analog)

#### I 180D33 IO domain (it depends on the voltage to determine whether it belongs to 1.8V domain/3V domain)

- n VDDIO\_SD1 (also no die domain)

#### I 3V domain

- n VDDIO\_SD0\_EMMC
- n VDD33A\_ETH\_\_USB

#### I DDR IO & DRAM domain

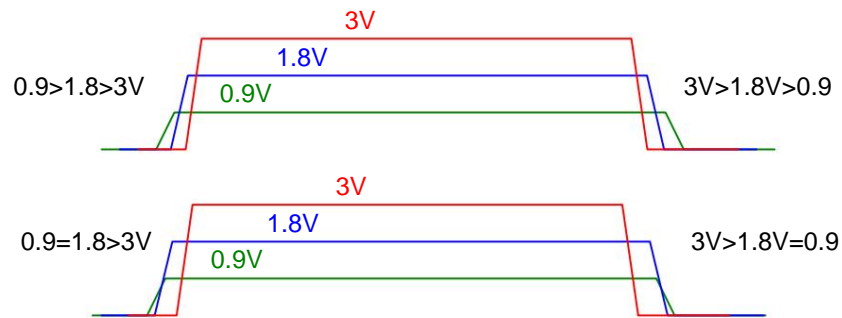
- n VDDQ



## n VDDQ\_DRAM

In principle, 0.9V and 1.8V can be powered on at the same time, or 0.9V first and then 1.8V, but **3V must be established before 1.8V**.

Power can only be powered on if the prerequisites are established. (Violation of the order may cause irreversible damage). Powering off is the reverse order of powering on.



Power-on and power-down behaviors that may

cause risks include: 1. When powering up, if VDD3 is >2V, VDD18 has not yet reached 1.8V-10%. This may cause damage to the 3V circuit. 2. When , VDD18 is lower than 1.8V-10%.

powering off, if VDD3 is <2V 3. When powering down, when VDD18>0.7V, but VDD09 is still below 0.5V, it may cause efuse malfunction. 4. When powering down, when VDD09<0.5V, VDD18 is still >0.5V cause efuse to malfunction.

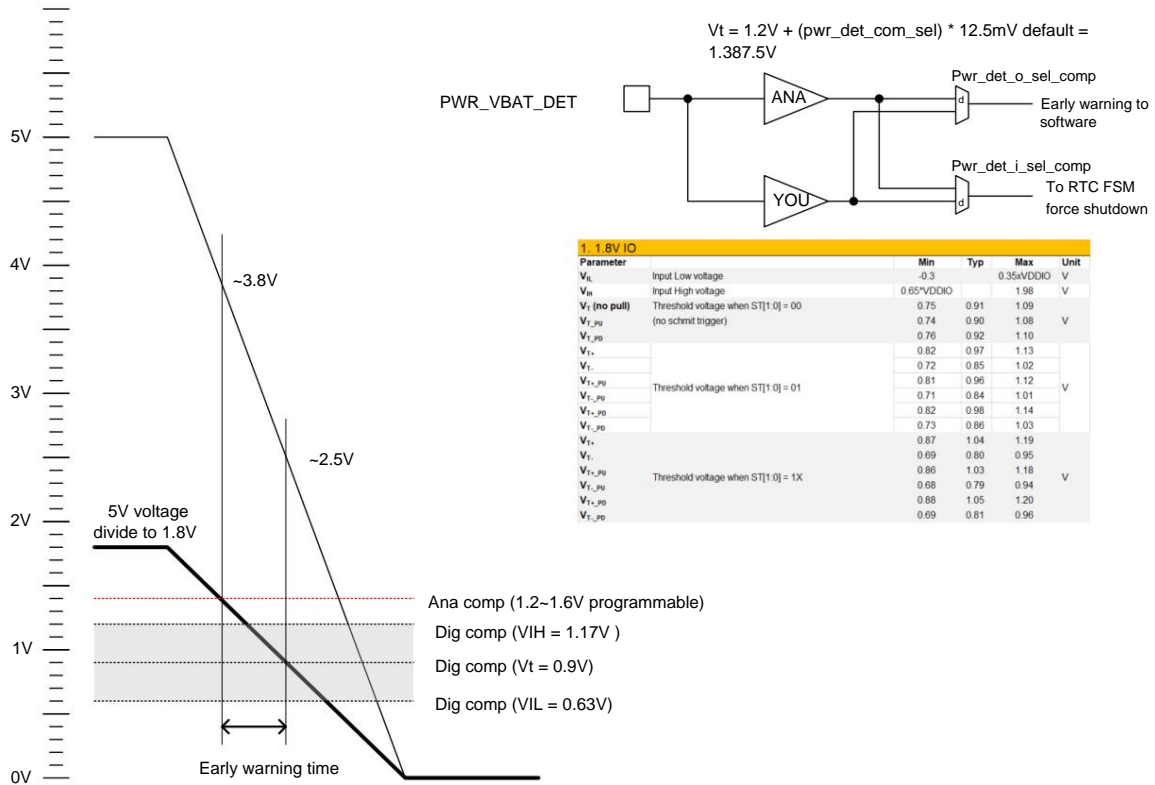
The chip has two pins PWR\_SEQ1 and PWR\_SEQ2 (VDDIO\_RTCdomain) to help control the power switch. The default SEQ1 is 0.9V & 1.8V. SEQ2 controls 3V. Some plug-in systems may use RC to determine the switch between 0.9V and 1.8V. .I only hope that the 3V of the chip still needs to be controlled by SEQ2 to avoid burning it.

SEQ1->SEQ2 when turning on

SEQ2->SEQ1 when turning off

PWR\_VBAT\_DET is used to detect the status of the main power supply. If the voltage is low, the software will receive an interrupt first (for example For example, stop writing to flash to prevent file system damage). If the voltage drops further, the RTC module will automatically start the power-off process.

PWR\_VBAT\_DET also needs to be logichigh to boot.



In actual use, the following four situations can be subdivided. The suggestions are as follows.

Power	Control	Plug-in applications(1) ExtRTC/noRTC	Plug-in applications(2) 32Kless
Main0.9V	Always on VDDC		VDDC
Main1.8V	Always on	VDD18A_AUD VDD18A_USB_PLL_ETH VDD18A_MIPI VDDIO_SD1 VDDIO_RTC	VDD18A_AUD VDD18A_USB_PLL_ETH VDD18A_MIPI
Main3.0V SEQ2		VDD33A_ETH_USB VDDIO_SD0_EMMC VDDIO_SD1	VDD33A_ETH_USB VDDIO_SD0_EMMC
MainVDDQ always on		VDDQ VDDQ_DRAM	VDDQ VDDQ_DRAM
VDDBACKUP	CoinBatt	ForexternalRTC	
V18RTC(lowiddqLDO)	Always on from CoinBatt		VDDIO_RTC VDDIO_SD1



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Power	Control	Battery Application(3) ExtRTC/noRTC	Battery Application(4) 32Kless
Main0.9V SEQ1		VDDC	VDDC
Main1.8V SEQ1		VDD18A_AUD VDD18A_USB_PLL_ETH VDD18A_MIPI	VDD18A_AUD VDD18A_USB_PLL_ETH VDD18A_MIPI
Main3.0V SEQ2		VDD33A_ETH_USB VDDIO_SD0_EMMC	VDD33A_ETH_USB VDDIO_SD0_EMMC
MainVDDQ SEQ2or3		VDDQ VDDQ_DRAM	VDDQ VDDQ_DRAM
VDDBACKUP CoinBatt		ForexternalRTC	
V18RTC(lowiddqLDO) Always on from Coinbatt		Noneed	VDDIO_RTC
VAO18	fromMain batt	WIFI otherAOdevice VDDIO_RTC VDDIO_SD1	WIFI otherAOdevice VDDIO_SD1
VAO33	fromMainbatt	WIFI otherAOdevice	WIFI otherAOdevice

### 2.5.5 Power supply DC/AC electrical parameters

sheet 2 7 SG2002 Power Supply Electrical Parameters (Recommended Operating Conditions)

Parameter		Min	Type	Max	Unit
VDDC	Corepower	0.81	0.9	0.99	IN
VDDC_RTC	CorepowerforRTCdomain(InternallDO,Caponly)	0.81	0.9	0.99	IN
VDD18A_AUD	AnalogpowerforAudioADC/DAC	1.62	1.8	1.98	IN
VDD18A_USB_PLL_ETH	AnalogpowerforEthernetPHY,USBPHY,PLL	1.62	1.8	1.98	IN
VDD18A_MIPI	AnalogpowerforMIPI	1.62	1.8	1.98	IN
VDD33A_ETH_USB	AnalogpowerforEthernetPHY,USBPHY	2.97	3.3	3.465	IN
VDDIO_SD0_EMMC	IOpowerforSD0&EMMCdomain	1.71 2.85	1.8 3.0/3.3	1.89 3.15/3.465	IN
VDDIO_SD1	IOpowerforSD1domain	1.71 2.85	1.8 3.0/3.3	1.89 3.465	IN


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Parameter		Min	Type	Max	Unit
<b>VDDIO_RTC</b>	IO power for RTC domain IO & LDO	1.3V	1.8	+10%	IN
<b>VDDQ</b>	IO & DRAM Power for DDR3L	1.283	1.35	1.417	IN
<b>VDDQ_DRAM</b>	IO & DRAM Power for DDR3	1.425	1.50	1.575	
	IO & DRAM Power for DDR2	1.425	1.50	1.575	
<b>Tjunc</b>	Junction Temperature (Max reduce from 125C due to DRAM)	-40	25	115 (note)	°C

Note. The guaranteed junction temperature of the DRAM used is only -40o C~115o C. Beyond this range, the content in the DRAM cannot be guaranteed to be complete.

Wholeness.



### 2.5.6 1.8V IO electrical parameters

Applicable domain(VDDIO18\_0,VDDIO18\_1,VDDIO18\_RM0,VDDIO\_RTC)

sheet **2 8 1.8VIO** Electrical parameters

Parameter		Min	Type	Max	Unit
WLL	InputLowvoltage	-0.3		0.35xVDDIO	IN
HIV	InputHighvoltage	0.65*VDDIO		1.98	IN
<b>VT (no pull)</b>		0.75	0.91	1.09	
VT_PU	ThresholdvoltagewhenST[1:0]=00(noschmitttrigger)	0.74	0.90	1.08	IN
VT_PD		0.76	0.92	1.10	
VT+		0.82	0.97	1.13	
VT-		0.72	0.85	1.02	
VT+_PU		0.81	0.96	1.12	
VT+_PD		0.71	0.84	1.01	IN
VT+_PD	ThresholdvoltagewhenST[1:0]=01	0.82	0.98	1.14	
VT+_PD		0.73	0.86	1.03	
VT+		0.87	1.04	1.19	
VT-		0.69	0.80	0.95	
VT+_PU		0.86	1.03	1.18	
VT+_PD		0.68	0.79	0.94	IN
VT+_PD	ThresholdvoltagewhenST[1:0]=1X	0.88	1.05	1.20	
VT+_PD		0.69	0.81	0.96	
~	Input leakage(VI =1.8Vor0V)			+/-10u	A
IOZ	Tri-stateoutputleakagecurrent(VO=1.8Vor0V)			+/-10u	A
RPU	Pullupresistor	55k	79k	121k	Oh
RPD	Pulldownresistor	51k	87k	169k	Oh
VOL	Outputlowvoltage			0.45	IN
VOH	Outputhighvoltage	1.35			IN
	Lowleveloutputcurrent@VOL (max)				
	DS[1:0]=00	7.6	12.8	18.0	mA
	DS[1:0]=01	15.2	25.3	35.5	mA
	DS[1:0]=10	22.6	37.4	52.2	mA
	DS[1:0]=11	29.7	49	67.9	mA
	Highleveloutputcurrent@VOH (max)				
	DS[1:0]=00	4.8	10.8	18.9	mA
	DS[1:0]=01	9.5	21.5	37.4	mA
	DS[1:0]=10	14.3	32.1	55.9	mA
	DS[1:0]=11	18.9	42.4	73.9	mA

### 2.5.7 18OD33 IO (VDDIO=1.8V) electrical parameters

Applicable domain(VDDIO\_EMMC,VDDIO\_SD0)

sheet **2 9 18OD33IO(VDDIO=1.8V)** Electrical parameters

Parameter		Min	Type	Max	Unit
WLL	Input LowVoltage	-0.3		0.58	IN



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Parameter		Min	Type	Max	Unit
HIW	Input high voltage	1.27		2.00	IN
<b>VT (no pull)</b>	Threshold voltage when ST=0 (no schmitt trigger)	0.91	0.97	1.03	IN
VT_PU		0.90	0.96	1.02	
VT_PD		0.91	0.97	1.06	
<b>VT+ (no pull)</b>	Threshold voltage when ST=1	1.03	1.07	1.12	IN
<b>VT- (no pull)</b>		0.75	0.83	0.91	
VT+_PU		1.02	1.06	1.11	
VT-_PU		0.74	0.82	0.90	
VT+_PD		1.03	1.08	1.13	
VT-_PD		0.75	0.83	0.92	
~	Input leakage (VI = 1.8V or 0V)			+/-10u	A
IOZ	Tri-state output leakage current (VO = 1.8V or 0V)			+/-10u	A
RPU	Pullup resistor	33k	60k	92k	Oh
RPD	Pulldown resistor	34k	61k	158k	Oh
VOL	Output low voltage			0.45	IN
VOH	Output high voltage	1.40			IN
IOL	Low level output current @ VOL (max)				
	DS[2:0]=000	4.9	7.8	11.1	mA
	DS[2:0]=001	7.4	11.7	16.4	mA
	DS[2:0]=010	9.8	15.5	21.7	mA
	DS[2:0]=011	12.2	19.2	26.7	mA
	DS[2:0]=100	14.6	23.0	31.9	mA
	DS[2:0]=101	17.0	26.6	36.8	mA
	DS[2:0]=110	19.4	30.2	41.6	mA
DS[2:0]=111	21.7	33.7	46.2	mA	
Ioh	High level output current @ VOH (max)				
	DS[2:0]=000	3.6	6.2	9.5	mA
	DS[2:0]=001	5.4	9.3	14.3	mA
	DS[2:0]=010	7.2	12.4	19.1	mA
	DS[2:0]=011	9.0	15.4	23.8	mA
	DS[2:0]=100	10.8	18.5	28.5	mA
	DS[2:0]=101	12.6	21.6	33.1	mA
	DS[2:0]=110	14.4	24.6	37.8	mA
DS[2:0]=111	16.2	27.7	42.5	mA	

## 2.5.8 18OD33 IO (VDDIO=3.0V) electrical parameters

Applicable domain (VDDIO\_EMMC, VDDIO\_SD0)

sheet 2 of 10 18OD33 IO (VDDIO=3.0V)

Electrical parameters

Parameter		Min	Type	Max	Unit
WLL	Input low voltage	-0.3		0.25*VDDIO	IN
HIW	Input high voltage	0.625*VDDIO		3.3	IN
<b>VT (no pull)</b>	Threshold voltage when ST=0 (no schmitt trigger)	0.82	0.95	1.11	IN
VT_PU		0.81	0.93	1.09	
VT_PD		0.83	0.96	1.13	
<b>VT+ (no pull)</b>	Threshold voltage when ST=1	1.00	1.10	1.23	IN



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Parameter		Min	Type	Max	Unit
<b>VT- (nopull)</b>		0.75	0.90	1.08	
VT+_PU		1.00	1.09	1.21	
VT-_PU		0.73	0.88	1.05	
VT+_PD		1.01	1.11	1.25	
VT-_PD		0.75	0.91	1.09	
~	Input leakage(VI =3.0Vor0V)			+/-10u	A
IOZ	Tri-stateoutputleakagecurrent(VO=3.0Vor0V)			+/-10u	A
RPU	Pullupresistor	33k	60k	93k	oh
RPD	Pulldownresistor	34k	62k	285k	oh
VOL	Outputlowvoltage			0.125*VDDIO	IN
VOH	Outputhighvoltage	0.75*VDDIO			IN
IOL	Lowleveloutputcurrent@ VOL (max)				
	DS[2:0]=000	3.1	5.5	8.6	mA
	DS[2:0]=001	4.7	8.2	12.7	mA
	DS[2:0]=010	6.2	10.8	16.9	mA
	DS[2:0]=011	7.7	13.4	20.8	mA
	DS[2:0]=100	9.3	16.1	24.9	mA
	DS[2:0]=101	10.8	18.7	28.8	mA
	DS[2:0]=110	12.3	21.2	32.6	mA
John	Highleveloutputcurrent@ VOH (max)				
	DS[2:0]=000	5.0	7.5	10.5	mA
	DS[2:0]=001	7.5	11.2	15.7	mA
	DS[2:0]=010	10.1	14.9	21.0	mA
	DS[2:0]=011	12.6	18.6	26.2	mA
	DS[2:0]=100	15.1	22.3	31.4	mA
	DS[2:0]=101	17.6	26.0	36.5	mA
	DS[2:0]=110	20.1	29.8	41.8	mA
DS[2:0]=111	22.6	33.4	46.9	mA	

## 2.5.9 Audio GPIO electrical parameters

sheet 2 of 11 AudioGPIO Electrical parameters

Parameter		Min	Type	Max	Unit
WLL	InputLowvoltage	-0.3		0.55	IN
HV	InputHighvoltage	1.2		1.98	IN
VT+	Thresholdvoltagewithschmitttrigger	0.8	0.95	1.1	IN
VT-		0.65	0.82	0.99	
~	Input leakage(VI =1.8Vor0V)			+/-4u	A
IOZ	Tri-stateoutputleakagecurrent(VO=1.8Vor0V)			+/-4u	A
VOL	Outputlowvoltage			0.4	IN
VOH	Outputhighvoltage	1.4			IN
IOL	Lowleveloutputcurrent@VOL (max)	4.9	9.9	18.4	mA
Iohn	Highleveloutputcurrent@ VOH (max)	11.3	17.1	26.1	mA

## 2.5.10 ETH GPIO electrical parameters

sheet 2 of 12 ETH GPIO Electrical parameters

Parameter		Min	Type	Max	Unit
WLL	InputLowvoltage	-0.3		0.3*VDD18A	IN
HV	InputHighvoltage	0.7*VDD18A		1.98	IN
VT+	Thresholdvoltagewithschmitttrigger	0.84	0.99	1.14	IN
VT-		0.66	0.83	1.01	
~	Input leakage(VI =1.8Vor0V)			+/-1.3u	A
IOZ	Tri-stateoutputleakagecurrent(VO=1.8Vor0V)			+/-1.3u	A
VOL	Outputlowvoltage			0.4	IN
VOH	Outputhighvoltage	VDD18A-0.4			IN
IOL	Lowleveloutputcurrent@VOL (max) DS=0	8.8	15.7	27.3	mA
	Lowleveloutputcurrent@VOL (max) DS=1	10.2	17.8	30.5	
Iohn	Highleveloutputcurrent@ VOH (max) DS=0	4.0	5.3	7.4	mA
	Highleveloutputcurrent@ VOH (max) DS=1	4.7	6.2	8.5	

## 2.5.11 MIPI Rx electrical parameters

The electrical parameters of MIPID-PHYHighSpeed (MIHS) are shown in Table 2-13 and Table 2-14.

The electrical parameters of MIPID-PHYLowPower (MILP) are shown in Table 2-15 and Table 2-16.

sheet 13. MIPID-PHY HighSpeed (MISH)2

difference DC Electrical parameters

參數	符號	資料速度	最小值	典型值	最大值	單位
Common Mode Voltage Range (VP+VM)/2	VCM(MIHS)	≤1.5Gbps	70	200	330	mV
		>1.5Gbps				
Internal Termination Resister Value	ZID(MIHS)	≤1.5Gbps	80	100	125	ohm
		>1.5Gbps				
Single-ended threshold for HS termination enable	VTERM-EN(MIHS)	≤1.5Gbps	--	--	450	mV
		>1.5Gbps				

sheet 2 14. MIPID-PHY HighSpeed (MIHS) differential AC electrical parameters

參數	符號	資料速度	最小值	典型值	最大值	單位
Differential Input Threshold Voltage (VP – VM)	VIDTH(MIHS)	≤1.5Gbps	-70	--	70	mV
		>1.5Gbps	-40	--	40	
Single-ended Input Voltage VP,VM	VIS(MIHS)	≤1.5Gbps	-40	--	460	mV
		>1.5Gbps				
Common-mode interface beyond 450MHz	ΔVCMRX	≤1.5Gbps	--	--	100	mV
		>1.5Gbps				
Common-mode interface 50MHz-450MHz	ΔVCMRX(LF)	≤1.5Gbps	-50	--	50	mV
		>1.5Gbps	-25	--	25	
Single-ended threshold for HS termination enable	VTERM-EN	≤1.5Gbps	--	--	450	mV
		>1.5Gbps				
Common-mode termination	CCM	≤1.5Gbps	--	--	60	pF
		>1.5Gbps				

sheet 2 15 MIPID-PHY LowPower (MILP)

difference DC Electrical parameters

參數	符號	最小值	典型值	最大值	單位
Logic 1 input voltage	VIHLP	740	--	--	mV
Logic 0 input voltage	VILLP	--	--	550	mV
Input hysteresis	VHYST	25	--	--	mV

## sheet 2 16 MIPID-PHY Low Power (MILP) Differential AC Electrical Parameters

參數	符號	最小值	典型值	最大值	單位
Input pulse rejection	eSPIKE	--	--	300	V·ps
Minimum pulse width response	TMIN-RX	20	--	--	ns
Peak interference amplitude	VINT	--	--	200	mV
Interference frequency	fINT	450	--	--	MHz

## 2.5.12 Sub-LVDS electrical parameters

The electrical parameters are shown in Table 2-17 and Table 2-18.

## sheet 2 17 Sub-LVDS(SL) difference DC Electrical parameters

參數	符號	最小值	典型值	最大值	單位
Common Mode Voltage Range ( $V_P + V_M$ )/2	VCM(SL)	600	900	1200	mV
Internal Termination Resistor Value	ZID(SL)	80	100	120	mV

## sheet 2 18 Sub-LVDS(SL) difference AC Electrical parameters

參數	符號	最小值	典型值	最大值	單位
Differential Input Threshold Voltage ( $V_P - V_M$ )	WIDTH(SL)	-70	--	70	mV
Single-ended Input Voltage $V_P, V_M$	VIS(SL)	400	--	1400	mV

## 2.5.13 HiSPi electrical parameters

HiSPi is divided into SLVS (HSSL) and HiVCM (HSHI), and their respective electrical parameters are shown in Table 2-19 and Table 2-20.

## sheet 2 19 HiSPi difference DC Electrical parameters

參數	符號	最小值	典型值	最大值	單位
Common Mode Voltage Range ( $V_P + V_M$ )/2	VCM(HSSL)	50	200	350	mV
	VCM(HSHI)	660	900	1170	
Internal Termination Resistor Value	ZID(HSSL)	80	100	125	mV
	ZID(HSHI)	80	100	125	

sheet **2 20** *HiSPI* difference **AC** Electrical parameters

參數	符號	最小值	典型值	最大值	單位
Differential Input Threshold Voltage (VP – VM)	VIDTH(HSSL)	-70	--	70	mV
	VIDTH(HSHI)	-100	--	100	
Single-ended Input Voltage VP, VM	VIS(HSSL)	-40	--	490	mV
	VIS(HSHI)	550	--	1350	

## 2.5.14 MIPI /LVDS Tx electrical parameters

sheet **2 21** *MIPI HS Transmitter DC Specifications*

Symbol	Description	Min	Type	Max	Units	Notes
VCMTX	HS transmit static common-mode voltage	150	200	250	mV	
$\bar{v}$ VCMTX(1,0)	VCMTX mismatch when output is Differential-1 or Differential-0	-	-	5	mV	
VOD	HS transmit differential voltage	140	200	270	mV	
$\bar{v}$ VOD	VOD mismatch when output is Differential-1 or Differential-0	-	-	14	mV	
VOHHS	HS output high voltage	-	-	360	mV	
ZOS	Single ended output impedance	40	50	62.5	$\Omega$	
$\bar{y}$ ZOS	Single ended output impedance mismatch	-	-	20	%	

sheet **2 22** *MIPI HS Transmitter AC Specifications*

Parameter	Description	Min	Type	Max	Units	Notes
$\bar{v}$ VCMTX(HF)	Common-level variations above 450MHz	-	-	15	mVRMS	
$\bar{v}$ VCMTX(LF)	Common-level variation between 50-450MHz	-	-	25	mVPEAK	
tR and tF	20%-80% rise time and fall time	-	-	0.3	UI	1,2
		-	-	0.35	UI	1,3
		100	-	-	ps	4

**Note:**

1. UI is unit interval. Example: 1 UI = 1 ns for 1 Gbps speed.
2. Applicable when supporting maximum HS bit rates  $\bar{y}$  1 Gbps (UI  $\bar{y}$  1 ns).
3. Applicable when supporting maximum HS bit rates  $\bar{y}$  1 Gbps (UI  $\bar{y}$  1 ns) but  $\bar{y}$  1.5 Gbps (UI  $\bar{y}$  0.667 ns).
4. Applicable when supporting maximum HS bit rates  $\bar{y}$  1.5 Gbps. However, to avoid excessive radiation, bit rates  $\bar{y}$  1 Gbps (UI  $\bar{y}$  1 ns), should not use values below 150 ps.

sheet **2 23** *MIPI LP Transmitter DC Specifications*

Parameter	Description	Min	Type	Max	Units	Notes
VOH	Thevenin output high level	1.1	1.2	1.3	IN	1
		0.95	-	1.3	IN	2





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Parameter	Description	Min	Type	Max	Units	Notes
VOL	Thevenin output low level	-50	-	50	mV	-
ZOLP	Output impedance of LP transmitter	110	-	-	oh	-

**Note:**

1. Applicable in normal Low Power mode when the supported data rate  $\leq$  1.5 Gbps.
2. Applicable in normal Low Power mode when the supported data rate  $>$  1.5 Gbps.

## sheet 2 24 MIPI LP Transmitter AC Specifications

Parameter	Description	Min	Type	Max	Units	Notes
TRLP/TFLP	15%-85% rise time and fall time	-	-	25	ns	-
TREOT	30%-85% rise time and fall time	-	-	35	ns	-
TLP-PULSE-TX	Minimum pulse width	20	-	-	ns	-
$\dot{V}/\dot{y}$ tSR	Slew rate @ CLOAD=0 to 70 pF (Falling Edge Only)	30	-	300	mV/ns 1	-
		25	-	300	mV/ns 2	-
CLOAD	Load capacitance	0	-	70	pF	-

**Note:**

1. Applicable in normal Low Power mode when the supported data rate  $\leq$  1.5 Gbps.
2. Applicable in normal Low Power mode when the supported data rate  $>$  1.5 Gbps.

## sheet 2 25 LVDS Transmitter DC/AC Specifications

Symbol	Description	Min	Type	Max	Units	Notes
V <sub>OUT</sub>	LVDS common mode offset voltage	1.125	1.25	1.375 V		
$ \dot{V}$ OS(1,0)	VOS mismatch when output is Differential-1 or Differential-0	-	-	-	mV	
V <sub>OD</sub>	LVDS transmit differential voltage	247	350	454	mV	
$ \dot{V}$ V <sub>OD</sub>	V <sub>OD</sub> mismatch when output is Differential-1 or Differential-0	-	-	50	mV	
TRLP/TFLP	15%-85% rise time and fall time (DUT side)	-	-	0.3UI	ns	

**2.5.15 SDIO electrical parameters**

EMMC/SD0/ SD1 Please refer to 2.5.7 and 2.5.8

**2.5.16 VI RAW/BT.601/BT.656/BT.1120 electrical parameters**

Please refer to 2.5.7 and 2.5.8 depending on the domain where the IO is located.





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### 2.5.17 BT.601/BT.656/8080 electrical parameters in VO (Video out)

Please refer to 2.5.7 and 2.5.8 depending on the domain where the IO is located.

### 2.5.18 AUDIO CODEC electrical parameters

sheet **2** **26 AudioCODEC** Overall indicator table

Parameter	Minimum value	Typical value	Maximum value	Unit	description
Analog Circuit Power Supply	1.62	1.8	1.98		IN
DEPARTMENT					
VREF		1.4/1.8			IN
		*VDD			

sheet **2** **27 AudioDAC** Electrical parameters

Parameter	Minimum value	Typical value	Maximum value	Unit	description
full output amplitude		1.55			Vpp maximum output signal swing

sheet **2** **28 Audio ADC** Electrical parameters

Parameter	Minimum value	Typical value	Maximum value	Unit	description
maximum input range		1.75			Vpp maximum input signal swing



## 2.6 Interface timing

### 2.6.1 SPI NOR interface timing

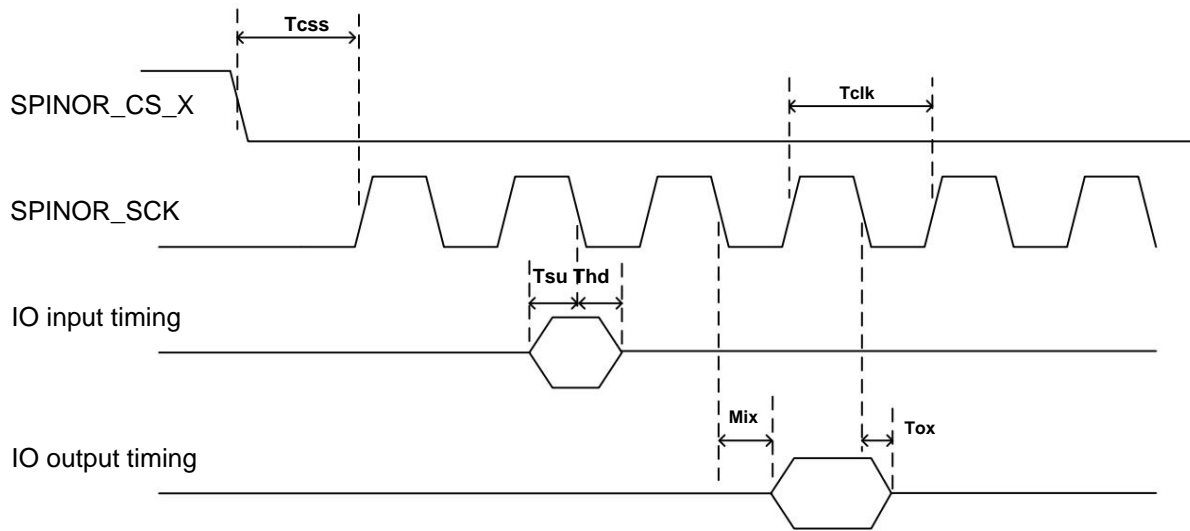


chart 2-7 SPINOR Interface timing diagram

\*IOinputtiming/IOoutputtimng means IOtiming used to transmit SPI\_NOR CMD/DATA under 1xI/O, 2xI/O, 4xI/O, which includes SPINOR\_SDI, SPINOR\_SDOySPINOR\_HOLD\_XySPINOR\_WP\_X

sheet 2 29 SPI\_NOR Interface timing parameter table

symbol	describe	Minimum	general	maximum CS	unit
Tcss	Negative edge to first clock edge time	13.4	Clock	-	ns
Tclk	cycle	13.4	Input signal setup time requirement	3.5	ns
Tsu	Input signal hold time requirement	0	Output signal	-	ns
Thd	valid delay	Output signal hold time	-	-	ns
Mix		-	-	2.6	ns
TOX		-1.5	-	-	ns



### 2.6.2 SPI NAND interface timing

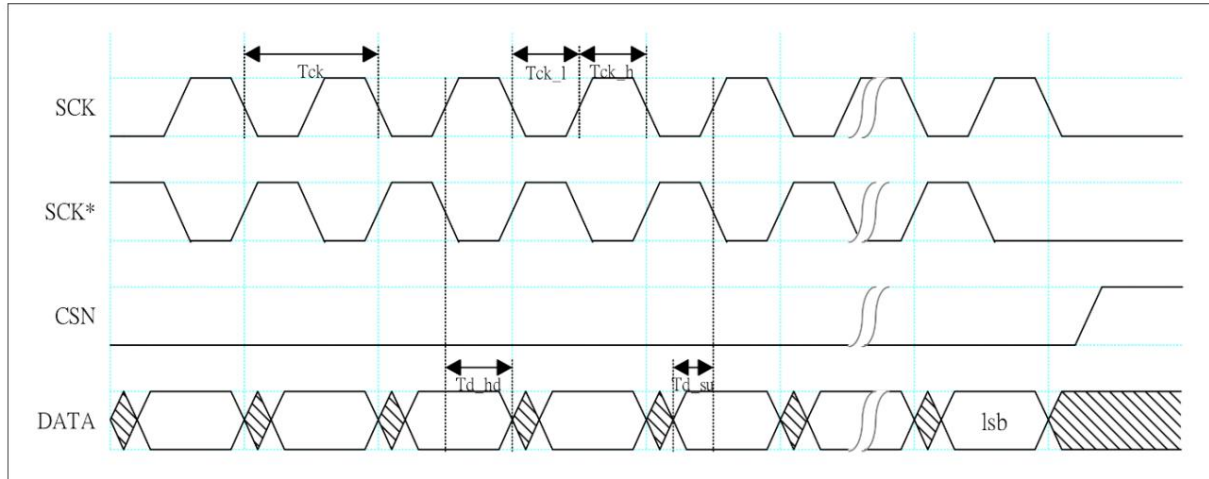


chart **2-8 SPINAND** Input direction timing diagram

sheet **2 30 SPINAND** Input direction timing

Parameter	Symbol	Minimum value	Typical value	Maximum value	Unit
	Tck	10.66		170.56	ns
clock cycle input signal setup time	Td_su	2.00	Td_hd		ns
requirements input signal hold time requirements	1.20				ns

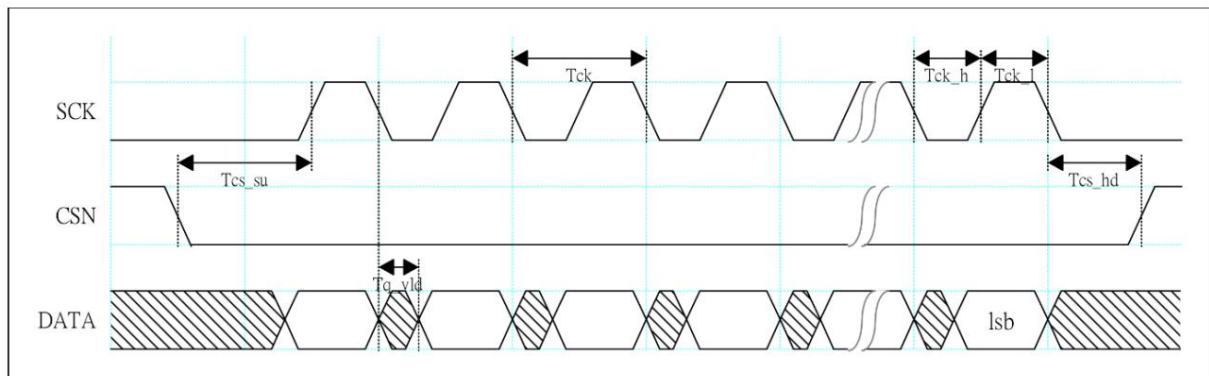


chart **2-9 SPINAND** Output direction timing diagram

sheet **2 31 SPINAND** Output direction timing

Parameter	Symbol	Minimum value	Typical value	Maximum value	Unit
cycle	Tck	10.66		170.56	ns


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	Symbol	Minimum value	Typical value	Maximum value	Unit
high	Tck_h	5.33		85.28	ns
level period clock low	Tck_l	5.33		85.28	ns
level period output <b>CS</b>	Tcs_su 10.66 Tcs_hd				ns
setup time output <b>CS</b>	10.66 Tq_vid -1.00				ns
hold time output signal delay				2.00	ns



### 2.6.3 VI interface timing

The VI interface timing sequence is shown in Figure 2-10.

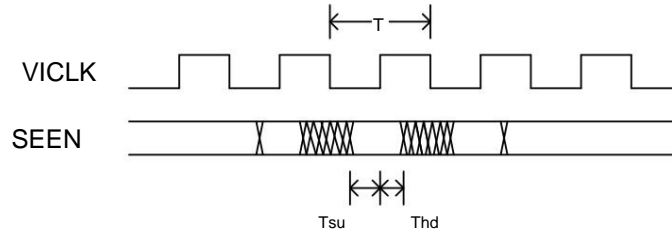


chart 2-10 VI Interface timing diagram

The VI interface timing parameters are shown in Table 2-32.

sheet 2-32 VI Interface timing parameter table

	Symbol	Min	Type	Max	Unit
VICLKclockcycle	T	6.73			ns
VIDATAsetuptime	Tsu	1.9			ns
VIDATAholdtime	Thd	0.8			ns

### 2.6.4 VO interface timing

The VO interface timing sequence is shown in Figure 2-11.

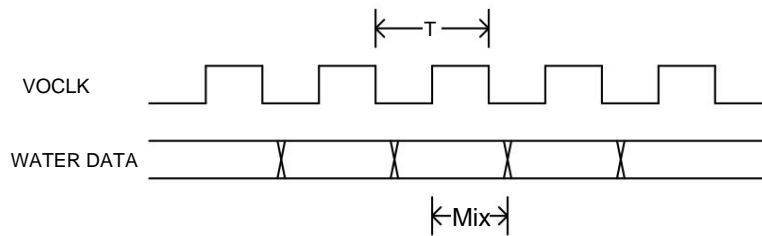


chart 2-11 VO Interface timing diagram

The VO interface timing parameters are shown in Table 2-33.



sheet 2 33 VO Interface timing parameter table

	Symbol	Min	Type	Max Unit	
VOCLKclockcycle	T		6.73		ns
VODATAdelaytime	Mix	T/2-1.5		T/2+1.5	ns

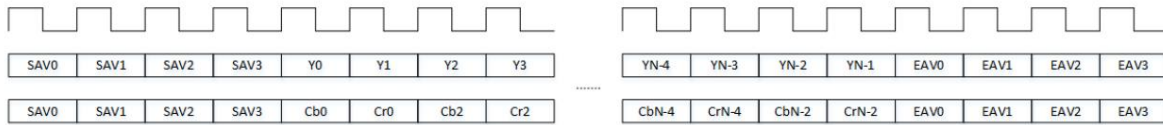


chart 2-12 BT.656 Interface timing diagram

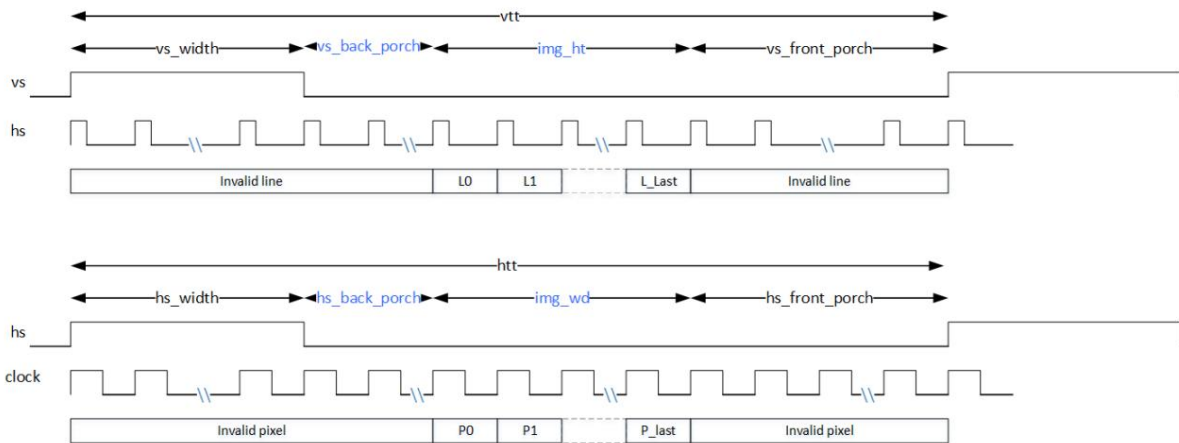


chart 2-13 BT.601 Interface timing diagram

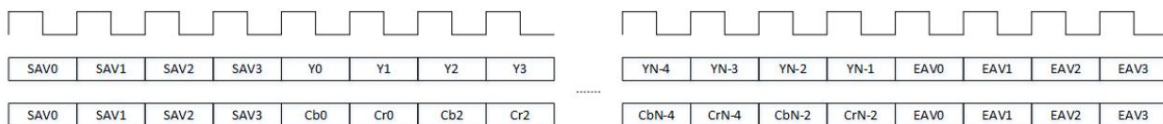


chart 2-14 BT.1120 Interface timing diagram

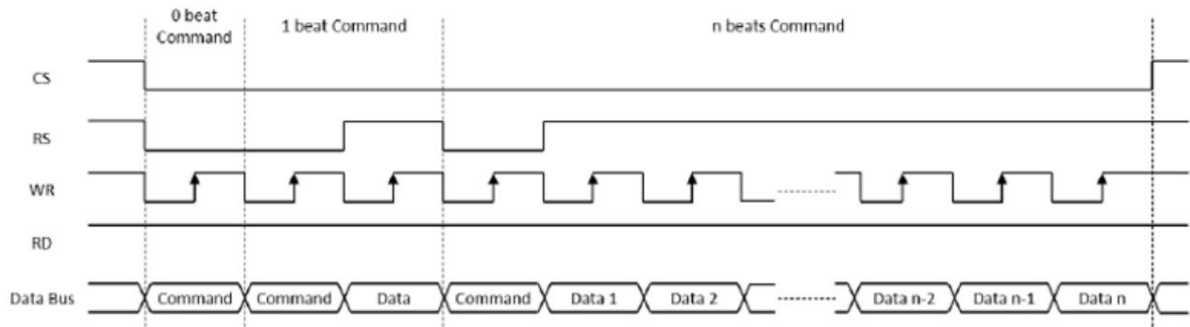


chart 2-15 8080 Interface timing diagram

### 2.6.5 AIAO (I2S/PCM) interface timing

When external AudioCodec is connected, the interface reception timing in I2S mode and PCM mode is shown in Figure 2-16.

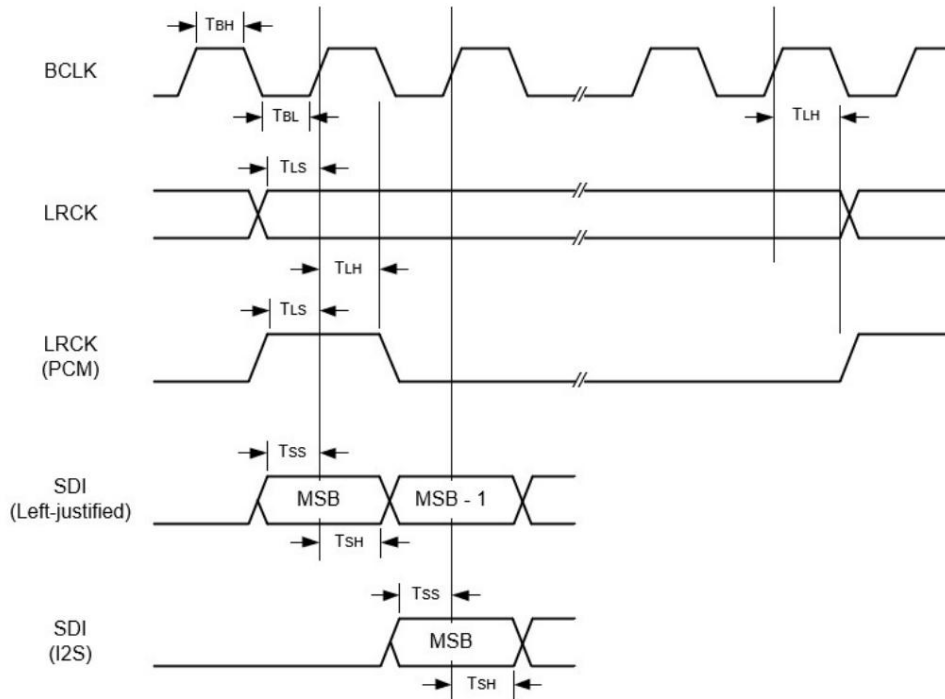


chart 2-16 I2S&PCM Interface receiving timing diagram

The interface sending timing in I2S mode and PCM mode is shown in Figure 2-17.

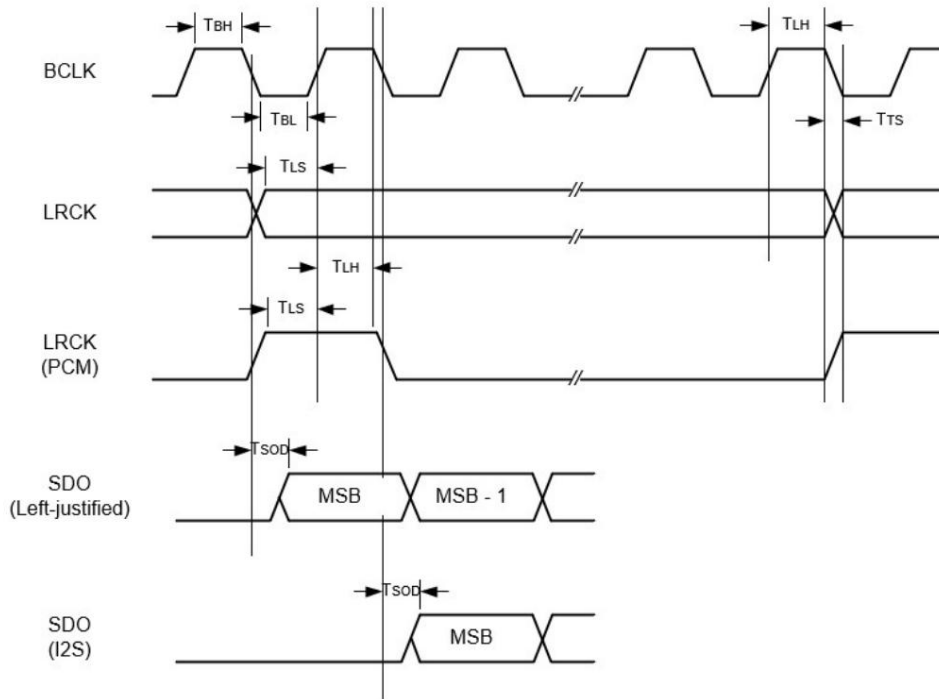


chart 2-17 I2S&PCM Interface sending timing diagram

The interface timing parameters are shown in Table 2-34.

sheet 34I2S/PCM 2 Interface timing parameter table

symbolic parameters		Minimum value	Typical value	Maximum value	Unit
TBL	BCLK low level pulse width (master mode and slave mode)	40	-	-	ns
TBH	BCLK high level pulse width (master mode and slave mode)	40	-	-	ns
TLS	LRCK setup time relative to BCLK rising edge (slave mode)	10	-	-	ns
TLH	LRCK hold time relative to BCLK rising edge (slave mode)	10	-	-	ns
TSS	SDI setup time relative to BCLK rising edge (master mode and slave mode)	10	-	-	ns
TSH	SDI hold time relative to BCLK rising edge (master mode and slave mode)	10	-	-	ns
TTS	BCLK falling edge clock skew relative to LRCK (Master mode)	0	-	10	ns
TSO	SDO signal delay time relative to BCLK falling edge (master mode and slave mode)	0	-	10	ns



## 2.6.6 I2C interface timing.

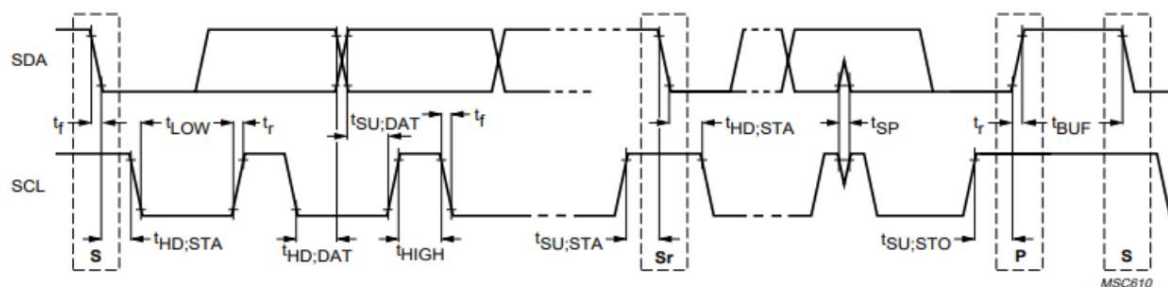


chart 2-18 I2C Interface timing diagram

sheet 2 35 I2C Interface timing parameter table

PARAMETER	SYMBOL	STANDARD-MODE		FAST-MODE		UNIT
		MIN.	MAX.	MIN.	MAX.	
SCL clock frequency	$f_{SCL}$	0	100	0	400	kHz
Hold time (repeated) START condition. After this period, the first clock pulse is generated	$t_{HD,STA}$	4.0	–	0.6	–	$\mu s$
LOW period of the SCL clock	$t_{LOW}$	4.7	–	1.3	–	$\mu s$
HIGH period of the SCL clock	$t_{HIGH}$	4.0	–	0.6	–	$\mu s$
Set-up time for a repeated START condition	$t_{SU,STA}$	4.7	–	0.6	–	$\mu s$
Data hold time: for CBUS compatible masters (see NOTE, Section 10.1.3) for I <sup>2</sup> C-bus devices	$t_{HD,DAT}$	5.0 0 <sup>(2)</sup>	– 3.45 <sup>(3)</sup>	– 0 <sup>(2)</sup>	– 0.9 <sup>(3)</sup>	$\mu s$ $\mu s$
Data set-up time	$t_{SU,DAT}$	250	–	100 <sup>(4)</sup>	–	ns
Rise time of both SDA and SCL signals	$t_r$	–	1000	$20 + 0.1C_b^{(5)}$	300	ns
Fall time of both SDA and SCL signals	$t_f$	–	300	$20 + 0.1C_b^{(5)}$	300	ns
Set-up time for STOP condition	$t_{SU,STO}$	4.0	–	0.6	–	$\mu s$
Bus free time between a STOP and START condition	$t_{BUF}$	4.7	–	1.3	–	$\mu s$
Capacitive load for each bus line	$C_b$	–	400	–	400	pF
Noise margin at the LOW level for each connected device (including hysteresis)	$V_{nL}$	$0.1V_{DD}$	–	$0.1V_{DD}$	–	V
Noise margin at the HIGH level for each connected device (including hysteresis)	$V_{nH}$	$0.2V_{DD}$	–	$0.2V_{DD}$	–	V



### 2.6.7 SPI interface timing

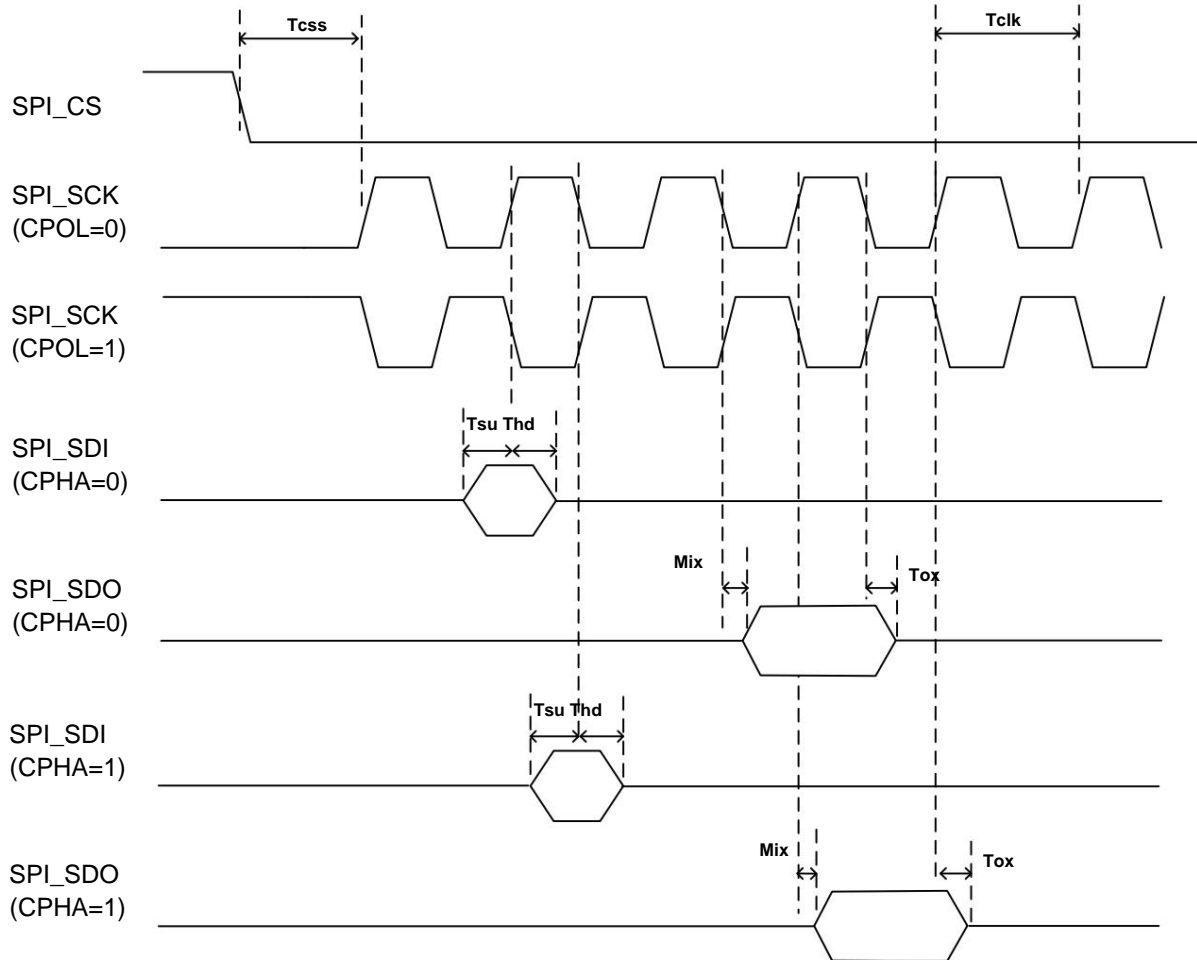


chart 2-19 SPI Interface timing diagram

sheet 2 36 SPI Interface timing parameter table

symbol		Minimum value	Typical value	Maximum value	Unit
$f_{clk}$	The SCK		-	46.8	MHz
$T_{css}$	frequency CS is 21.4 from the negative edge to the		-	-	ns
$T_{clk}$	first clock edge. The clock cycle is 21.4. The input		-	-	ns
$T_{su}$	signal setup time requirement is 9.5. The input		-	-	ns
$T_{hd}$	signal hold time requirement is 0. The output		-	-	ns
$Mix$	signal valid delay is the output		-	3	ns
$TOX$	signal hold time.	-3	-	-	ns



## 2.6.8 MIPI Rx interface timing

The speed range of MIPI Rx is 0.08Gbps to 1.5Gbps

A. 0.08Gbps to 1.5Gbps

The timing diagram is shown in Figure 2-20, and the timing parameters are shown in Table 2-37

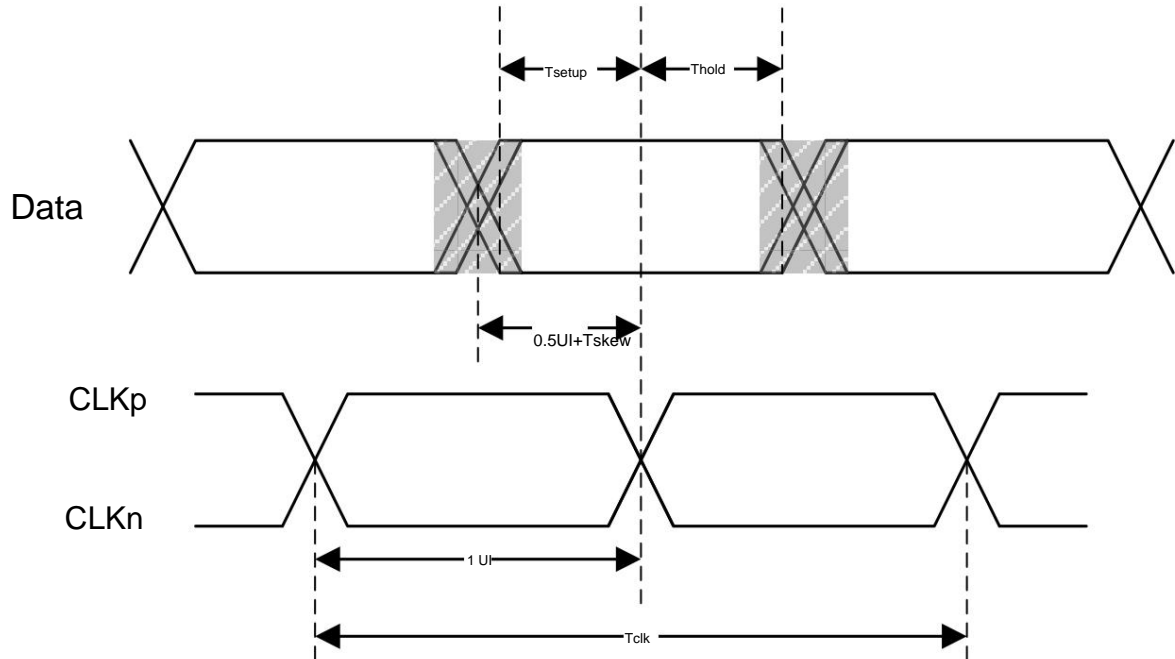


chart 2-20. MIPI Rx exist 0.08Gbps to 1.5Gbps clock data timing diagram

sheet 2-37 MIPI Rx exist 0.08Gbps to 1.5Gbps Timing parameter table

參數	符號	資料速度區間	最小值	典型值	最大值	單位
資料速度	Data Rate	$0.08\text{G} \leq \text{Data Rate} \leq 1\text{G}$	0.08		1	Gbps
		$1\text{G} < \text{Data Rate} \leq 1.5\text{G}$	1		1.5	
差分時鐘週期	Tclk	$0.08\text{G} \leq \text{Data Rate} \leq 1\text{G}$	2		25	ns
		$1\text{G} < \text{Data Rate} \leq 1.5\text{G}$	1.33		2	
發射端資料到時鐘歪斜時間	$T_{\text{SKEW}}$	$0.08\text{G} \leq \text{Data Rate} \leq 1\text{G}$	-0.15		0.15	UIHS *
		$1\text{G} < \text{Data Rate} \leq 1.5\text{G}$	-0.2		0.2	
接收端差分時鐘建立時間	$T_{\text{SETUP}}$	$0.08\text{G} \leq \text{Data Rate} \leq 1\text{G}$	0.15			UIHS
		$1\text{G} < \text{Data Rate} \leq 1.5\text{G}$	0.2			
接收端差分時鐘保持時間	$T_{\text{HOLD}}$	$0.08\text{G} \leq \text{Data Rate} \leq 1\text{G}$	0.15			UIHS
		$1\text{G} < \text{Data Rate} \leq 1.5\text{G}$	0.2			
* UIHS = $1/\text{資料速度} = \text{差分時鐘週期}/2$						

## 2.6.9 Sub-LVDS interface timing

The Sub-LVDS clock data timing diagram is shown in Figure 2-21, and the timing parameters are shown in Table 2-38

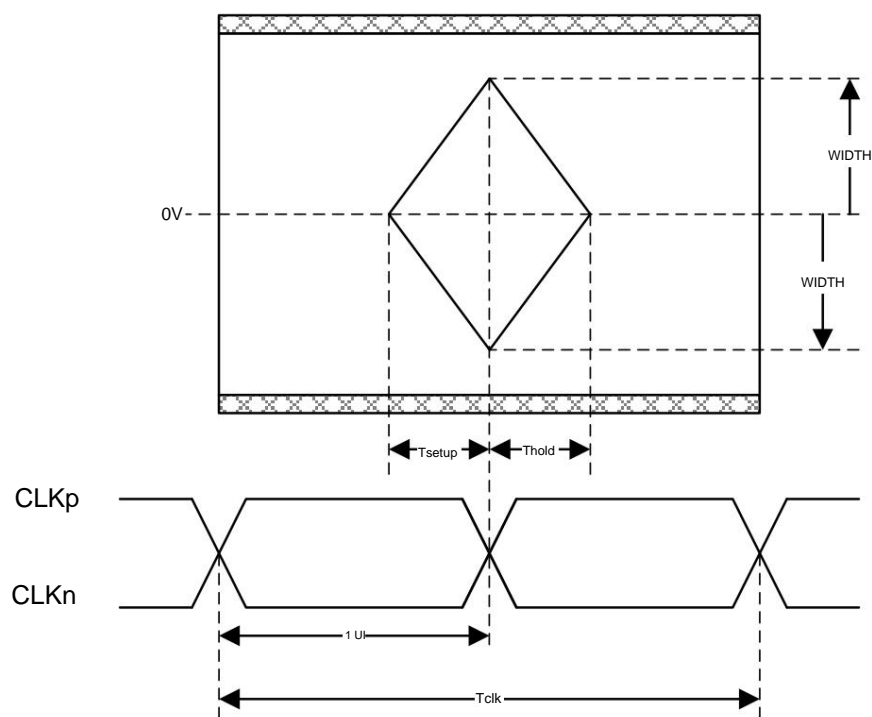


chart 2-21. Sub-LVDS Clock data timing diagram

sheet 2 38. Sub-LVDS Timing parameter table

參數	符號	最小值	典型值	最大值	單位
資料速度	Data Rate	--	--	1.5	Gbps
位元標準時間	UI	666.6	--	--	ns
差分時鐘週期	Tclk	1333.3	--	--	ns
接收端差分時鐘建立時間	T <sub>SETUP</sub>	0.15	--	--	UI
接收端差分時鐘保持時間	T <sub>HOLD</sub>	0.15	--	--	UI
Differential Input Threshold Voltage (V <sub>P</sub> - V <sub>M</sub> )	WIDTH(SL)	-70	--	70	mV
* UI = 1 / 資料速度 = 差分時鐘週期 / 2					



## 2.6.10 HiSPi interface timing

The HiSPi clock data timing diagram is shown in Figure 2-22, and the timing parameters are shown in Table 2-39

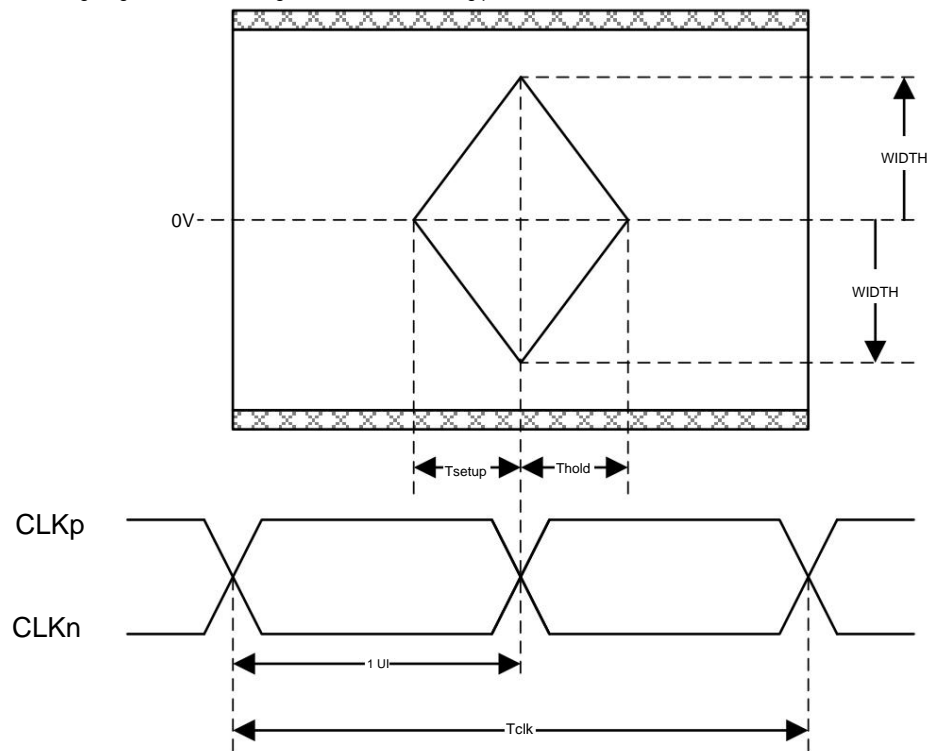


chart 2-22. HiSPi Clock data timing diagram

sheet 239. HiSPi Timing parameter table

參數	符號	最小值	典型值	最大值	單位
資料速度	Data Rate	--	--	1.5	Gbps
位元標準時間	UI	666.6	--	--	ns
差分時鐘週期	Tclk	1333.3	--	--	ns
接收端差分時鐘建立時間	$T_{SETUP}$	0.15	--	--	UI
接收端差分時鐘保持時間	$T_{HOLD}$	0.15	--	--	UI
Differential Input Threshold Voltage (VP-VM)	WIDTH(HSSL)	-70	--	70	mV
	WIDTH(HSHI)	-100	--	100	
* UI= 1/資料速度 = 差分時鐘週期/2					

### 2.6.11 MIPI Tx interface timing

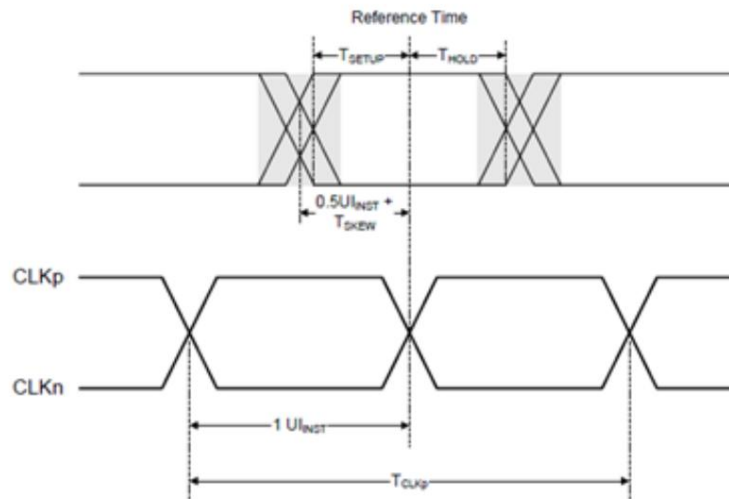


chart 2-23 **MIPITX** Interface data versus clock timing diagram

#### sheet 2 40 Data-Clock Timing Specifications for 0.08Gbps and 1Gbps

Symbol	Description	Min	Name	Max	Units	Notes
TSKEW[TX]	TX Data to Clock Skew	-0.15		0.15	UIHS	

#### sheet 2 41 Data-Clock Timing Specifications for >1Gbps and 1.5Gbps

Symbol	Description	Min	Name	Max	Units	Notes
TSKEW[TX]	TX Data to Clock Skew	-0.2		0.2	UIHS	

#### sheet 2 42 Data-Clock Timing Specifications for >1.5Gbps and 2.5Gbps

Symbol	Description	Min	Name	Max	Units	Notes
TSKEW[TX]	TX Data to Clock Skew	-0.2		0.2	UIHS	
TJX	TX Data to Clock Total Jitter			0.3	UIHS	
DJTX	TX Data to Clock Deterministic Jitter			0.2	UIHS	
RJTX	TX Data to Clock Random Jitter			0.1	UIHS	

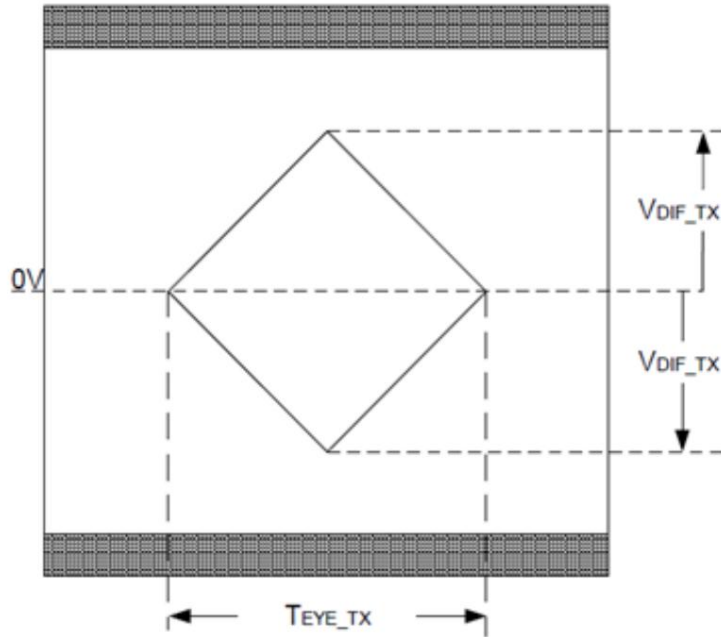


chart **2-24 TXEYE Diagram Specification**

sheet **2 43 Transmitter Eye Diagram Specification**

Bit Error Rate	$T_{EYE\_TX}$	$V_{DIF\_TX}$
$10^{-12}$	0.5UI	40mV
$10^{-6}$ (Prorated for Validation)	0.53UI	47mV

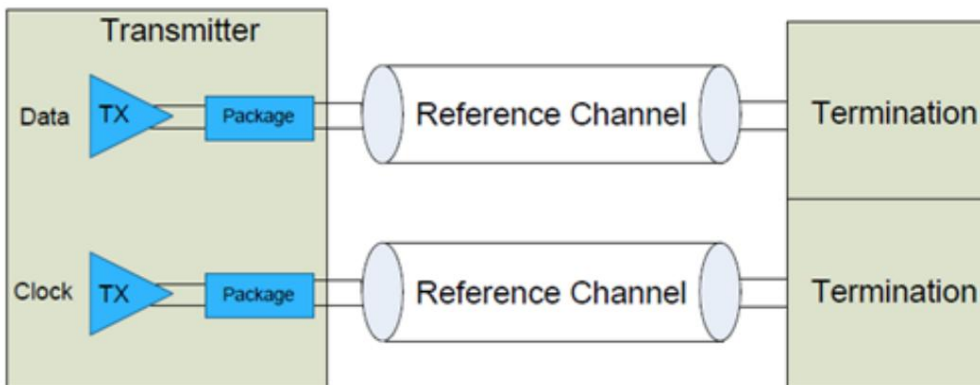


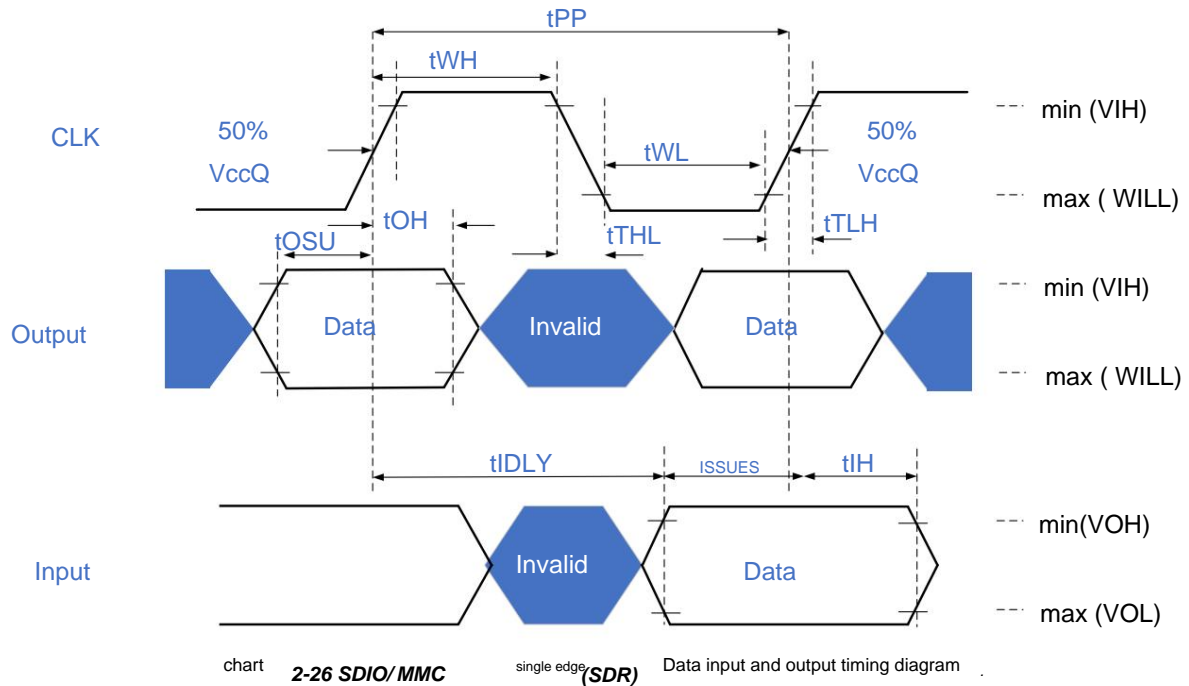
chart **2-25 Transmitter Eye Diagram Validation Setup**





### 2.6.12 SDIO/MMC interface timing

The data input and output direction timing sequence of a single edge is shown in Figure 2-26.



sheet **2** **44 SDIO/MMC** single edge **DS(defaultspeed)** Mode timing parameter table

parameter	Symbol	Minimum value	Typical value	Maximum value	Unit	Remarks
<b>ClockCLK</b>						
<b>Clockfrequency</b>	fPP	0	-	26	MHz	fpp=1/tpp
<b>Data transfer mode</b>						CL $\dot{y}$ 30pF
<b>Clockfrequency</b>	fOD	0	-	400	KHz	CL $\dot{y}$ 30pF
<b>IdentificationMode</b>						
<b>Clockhightime</b>	tWH 10		-	-	ns	CL $\dot{y}$ 30pF
<b>Clocklowtime</b>	tWL	10	-	-	ns	CL $\dot{y}$ 30pF
<b>Clockrisetime</b>	tTLH	-	-	10	ns	CL $\dot{y}$ 30pF
<b>Clockfalltime</b>	tTHL	-	-	10	ns	CL $\dot{y}$ 30pF
<b>InputsCMD,DAT(referencedtoCLK)</b>						
<b>Inputset-uptime</b>	ISSUES	6	-	-	ns	CL $\dot{y}$ 30pF
<b>Inputholdtime</b>	tIH	8.3	-	-	ns	CL $\dot{y}$ 30pF
<b>OutputsCMD,DAT(referencedtoCLK)</b>						





parameter	Symbol	Minimum value	Typical value	Maximum value	Unit	Remarks
<b>Outputset-uptime</b> tOSU 5					ns	CL $\dot{y}$ 30pF
<b>Outputholdtime</b> tOH 5					ns	CL $\dot{y}$ 30pF

sheet **45 SDIO/MMC2** single edge **HS(Highspeed)** Mode timing parameter table

parameter	Symbol	Minimum value	Typical value	Maximum value	Unit	Remarks
<b>ClockCLK</b>						
<b>Clockfrequency</b>	fpp	0		52	MHz	fpp=1/tp
<b>Data transfer mode</b>						CL $\dot{y}$ 30pF
<b>Clockhightime</b>	tWH 6.5				ns	CL $\dot{y}$ 30pF
<b>Clocklowtime</b>	tWL 6.5				ns	CL $\dot{y}$ 30pF
<b>Clockrisetime</b>	tTLH			3	ns	CL $\dot{y}$ 30pF
<b>Clockfalltime</b> tTHL				3	ns	CL $\dot{y}$ 30pF
<b>InputsCMD,DAT(referencedtoCLK)</b>						
<b>Inputset-uptime</b> tISU		6			ns	CL $\dot{y}$ 30pF
<b>Inputholdtime</b>	tIH	2.5			ns	CL $\dot{y}$ 30pF
<b>OutputsCMD,DAT(referencedtoCLK)</b>						
<b>Outputset-uptime</b> tOSU 6					ns	CL $\dot{y}$ 30pF
<b>Outputholdtime</b> tOH 3					ns	CL $\dot{y}$ 30pF

The data input and output direction timing sequence of double edges is shown in Figure 2-27.

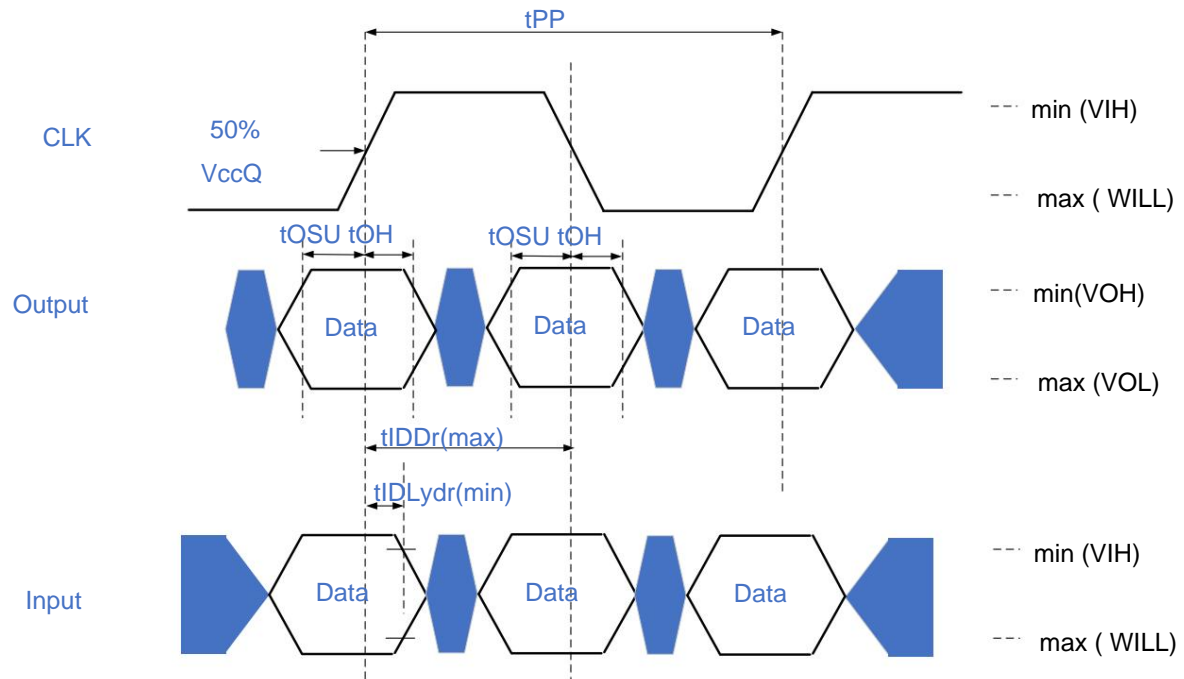


chart **2-27 SDIO/MMC** Double edge **DDR50** Pattern data input and output direction timing diagram



sheet 46 SDIO/MMC2 Double edge DDR50 Mode timing parameter table

parameter	symbol	most Small value	typical value	most big value	Unit	remarks
<b>ClockCLK</b>						
<b>ClockfrequencyDatatransferMode</b>	fP	0		52 MHz		fpp=1/tp CL <sub>y</sub> 30pF
<b>InputsDAT(referencedtoCLK)</b>						
<b>Input delay time during data transfer</b>	t <sub>IDL</sub> YDr 1.5			7	ns	CL <sub>y</sub> 20pF
<b>OutputsDAT(referencedtoCLK)</b>						
<b>Outputset-uptime</b>	t <sub>OSU</sub>	3			ns	CL <sub>y</sub> 20pF
<b>Outputholdtime</b>	t <sub>OH</sub>	2.5			ns	CL <sub>y</sub> 20pF

The data input and output direction timing sequences of HS200 and SDR104 are shown in Figure 2-28.

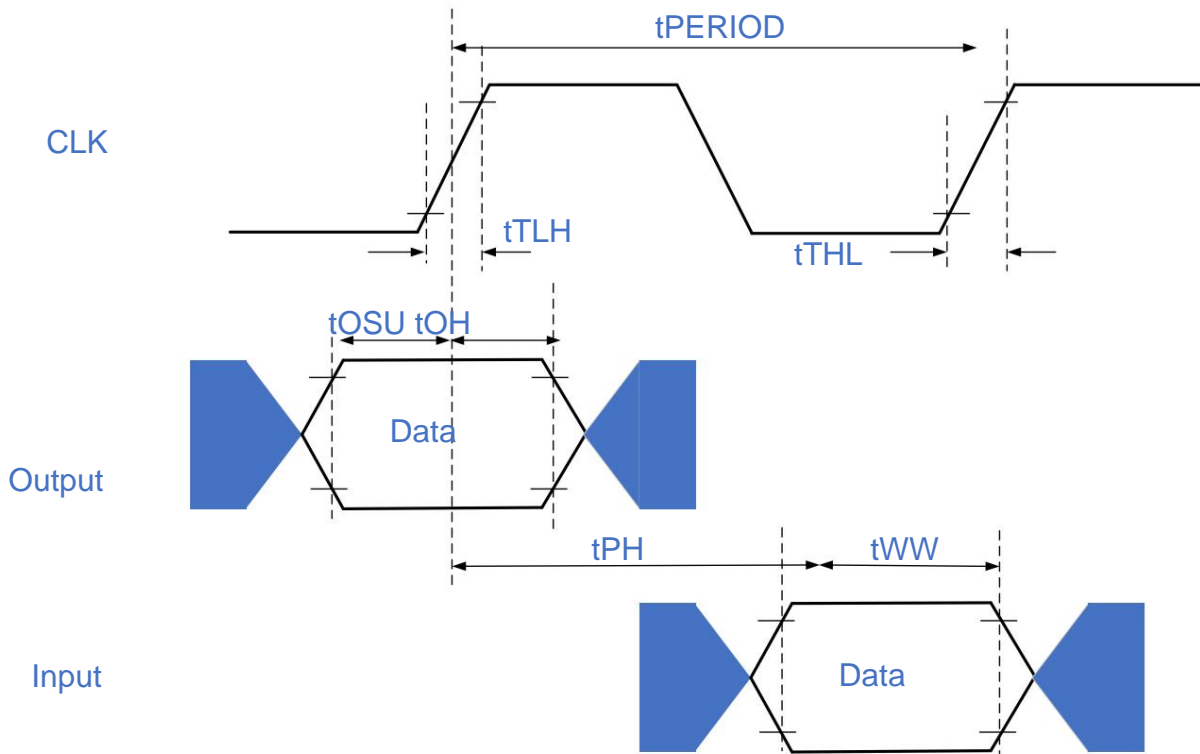


chart 2-28 SDIO/MMCHS200 and SDR104 Pattern data command output direction timing diagram

sheet 2 47 SDIO/MMCHS200 and SDR104 Mode output parameter table

parameter	symbol	smallest value	Typical value	Maximum value	Unit	Remarks
<b>Outputset-uptime</b>	TOSU 1.4	-			ns	CDEVICEy6pF

 <b style="font-size: 1.2em; vertical-align: middle;">SOPHON</b> Specifications are subject to change without notice	SG2002 <i>Preliminary Datasheet</i>
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parameter	symbol	smallest value	Typical value	Maximum value	Unit	Remarks
<b>Output hold time</b>	tOH	0.8	-	-	ns	

sheet **2** **48 SDIO/MMCHS200** and **SDR104** Mode input timing parameter table

parameter	symbolic minimum	symbolic maximum	typical value	Maximum value	unit	remarks
<b>Phase difference between device TX CMD/DAT and RX CLK</b>	tPH	0	-	2	UI	Unit Interval (UI) is one bit nominal time. For 200MHz UI=5ns
<b>Input valid data window</b>	tWW	0.575	-	-	UI	TVW=2.88ns at 200MHz



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